

## Zero-Drift, 65V High-Side Current Sense Amplifier

### Features

- Single Amplifier: MCP6C02
- Bidirectional or Unidirectional
- Input (Common-mode) Voltages:
  - +3.0V to +65V, specified
  - +2.8V to +68V, operating
  - -0.3V to +70V, survival
- Power Supply:
  - 2.0V to 5.5V
  - Single or Dual (Split) Supplies
- High DC Precision
  - $V_{OS}$ :  $\pm 1.65 \mu\text{V}$  (typical)
  - CMRR: 154 dB (typical)
  - PSRR: 138 dB (typical)
  - Gain Error:  $\pm 0.1\%$  (typical)
- Preset Gains: 20, 50 and 100 V/V
- POR Protection
  - HV POR for  $V_{IP} - V_{SS}$
  - LV POR for  $V_{DD} - V_{SS}$
- Bandwidth: 500 kHz (typical)
- Supply Current: 490  $\mu\text{A}$  (typical)
- Enhanced EMI Protection:
  - EMIRR: 118 dB at 2.4 GHz (typical)
- Extended Temperature Range (E-Temp):
  - $-40^\circ\text{C}$  to  $+125^\circ\text{C}$

### Typical Applications

- Motor Control
- Analog Level Shifter
- Industrial Computing
- Battery Monitor/Tester

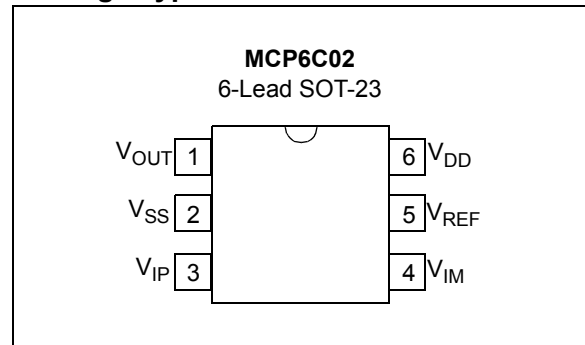
### General Description

The Microchip Technology Inc. MCP6C02 high-side current sense amplifier is offered with preset gains of 20, 50 and 100 V/V. The Common-mode input range ( $V_{IP}$ ) is +3V to +65V. The differential-mode input range ( $V_{DM} = V_{IP} - V_{IM}$ ) supports unidirectional and bidirectional applications.

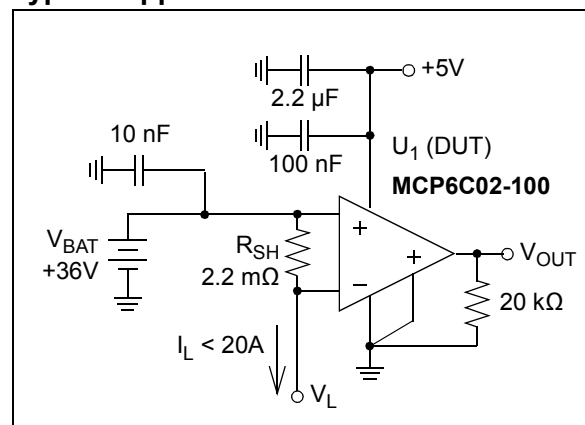
The power supply can be set between 2.0V and 5.5V. This device is specified from  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$  (E-Temp) and is provided in the SOT-23 package.

The Zero-Drift architecture supports very low input errors, which allow a design to use shunt resistors of lower value (and lower power dissipation).

### Package Types

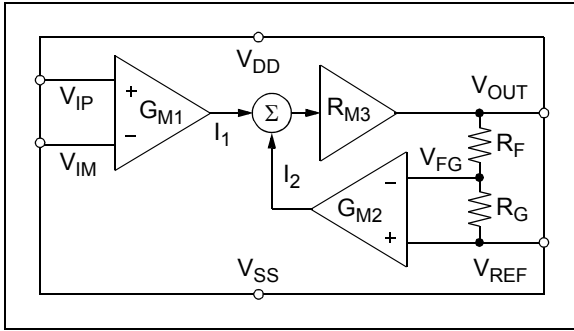


### Typical Application Circuit



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## Functional Diagram



## Gain Options

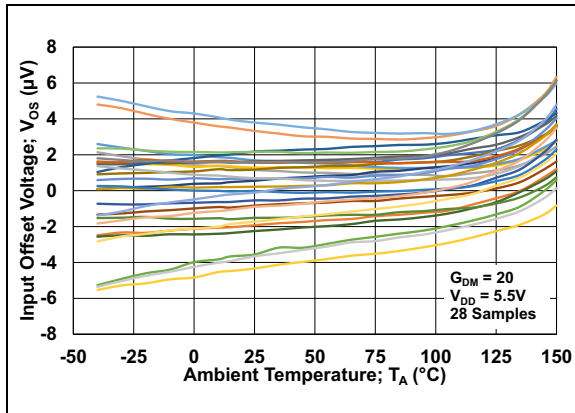
Table 1 shows key specifications that differentiate between the three different differential gain ( $G_{DM}$ ) options. See [Section 1.0 “Electrical Characteristics”](#), [Section 6.0 “Packaging Information”](#) and [Product Identification System](#) for further information on the GDM options available.

**TABLE 1: KEY DIFFERENTIATING SPECIFICATIONS**

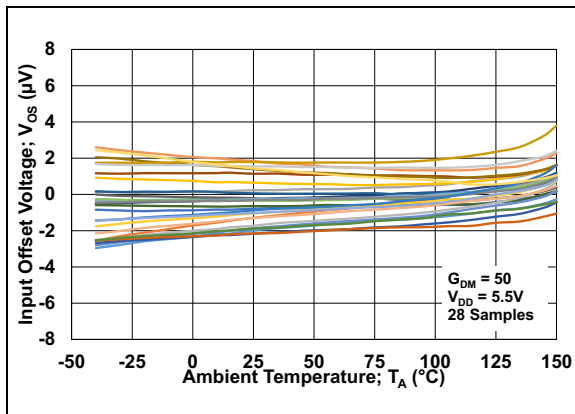
Part No.	$G_{DM}$ (V/V) Nom.	$V_{OS}$ ( $\pm \mu V$ ) Max.	$TC_1$ ( $\pm nV/^\circ C$ ) Max.	CMRR (dB) Min.	PSRR (dB) Min.	$V_{DMH}$ (V) Min.	BW (kHz) Typ.	$E_{ni}$ ( $\mu V_{p-p}$ ) Typ.	$e_{ni}$ (nV/ $\sqrt{Hz}$ ) Typ.
MCP6C02-020	20	16	90	132	109	0.265	500	1.54	74
MCP6C02-050	50	14	70		115	0.106		0.95	46
MCP6C02-100	100	12	65		116	0.053	390	0.92	44

- Note 1:**  $V_{OS}$  and  $TC_1$  limits are by design and characterization only.  
**Note 2:**  $TC_1$  covers the Extended Temperature Range (-40°C to +125°C).  
**Note 3:** CMRR is at  $V_{DD} = 5.5V$ .  
**Note 4:**  $E_{ni}$  is at  $f = 0.1 \text{ Hz}$  to  $10 \text{ Hz}$ .  $e_{ni}$  is at  $f < 500 \text{ Hz}$ .

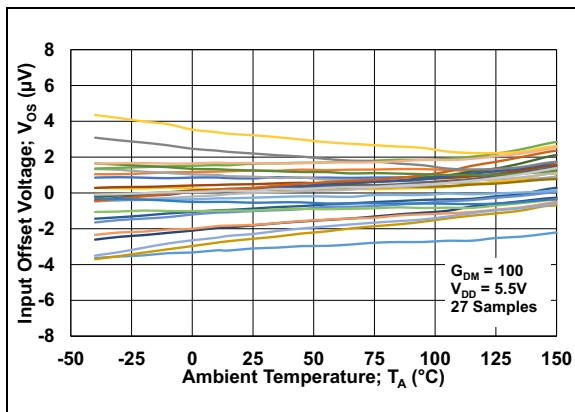
Figure 1, Figure 2 and Figure 3 show input offset voltage versus temperature for the three gain options ( $G_{DM} = 20, 50$  and  $100$  V/V).



**FIGURE 1:** Input Offset Voltage vs. Temperature,  $G_{DM} = 20$  V/V.

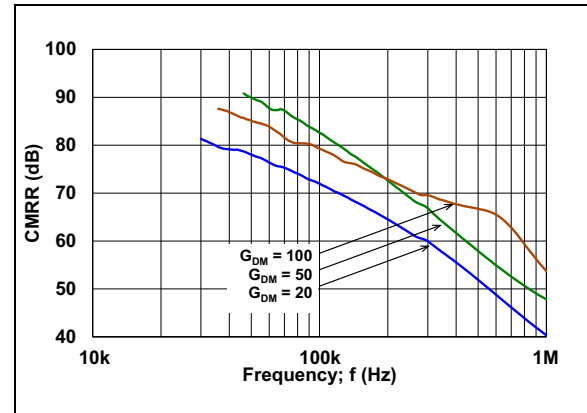


**FIGURE 2:** Input Offset Voltage vs. Temperature,  $G_{DM} = 50$  V/V.



**FIGURE 3:** Input Offset Voltage vs. Temperature,  $G_{DM} = 100$  V/V.

The MCP6C02's CMRR supports applications in noisy environments. Figure 4 shows how CMRR is high, even for frequencies near 100 kHz.



**FIGURE 4:** CMRR vs. Frequency.

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NOTES:

## 1.0 ELECTRICAL CHARACTERISTICS

### 1.1 Absolute Maximum Ratings †

$V_{DD} - V_{SS}$ .....	-0.3V to +5.5V
Current at Input Pins (Note 1) .....	±2 mA
Analog Inputs ( $V_{IP}$ and $V_{IM}$ ) (Note 1) .....	-0.3V to +70V
All Other Inputs and Outputs .....	$V_{SS} - 0.3V$ to $V_{DD} + 0.3V$
Input Difference Voltage ( $V_{DM}$ ) .....	±1.2V
Output Short-Circuit Current .....	Continuous
Current at Output and Supply Pins .....	±30 mA
Storage Temperature .....	-65°C to +150°C
Maximum Junction Temperature .....	+155°C
ESD protection pins (HBM, CDM, MM) .....	≥ 2 kV, 2 kV, 300V

† **Notice:** Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

**Note 1:** These voltage and current ratings are physically independent; both conditions must be enforced by the user.

### 1.2 Voltage and Temperature Ranges

The various voltage and temperature ranges are listed in [Table 1-1](#).

**TABLE 1-1: VOLTAGE AND TEMPERATURE RANGES**

Parameter	Units	$G_{DM}$ (V/V)	Comment	Range				
				Type	Sym.	Spec.	Oper.	Abs. Min./Max.
$V_{DD}$ (Note 2)	V	All	$V_{DD} \uparrow$ (LV POR on)	Min.	$V_{DDL}$	2.0	1.7	-0.3
			$V_{DD} \downarrow$ (LV POR on)		$V_{DDL D}$	1.05	—	
			LV POR Hysteresis		$V_{DDL H}$	0.1	—	
			—		Typ.	—	2.0 to 5.5	
			—	Max.	$V_{DDH}$	5.5	5.5	5.5
$V_{IP}$ (Note 2)	V	All	$V_{IP} \uparrow$ (HV POR on)	Min.	$V_{IPL}$	3.0	2.8	-0.3
			$V_{IP} \downarrow$ (HV POR on)		$V_{IPL D}$	2.8	2.6	
			HV POR Hysteresis		$V_{IPL H}$	0.2 Typ.	0.2 Typ.	
			—		Typ.	—	34	
			—	Max.	$V_{IPH}$	65	68	70

**Note 1:** All of this table's limits are set by design and characterization.

**2:** The HV POR is triggered by  $V_{IP}$ , with hysteresis. The LV POR is triggered by  $V_{DD}$ , with hysteresis.

**3:**  $V_{DM} = V_{IP} - V_{IM}$ .  $V_{IM}$  is in its range when both  $V_{IP}$  and  $V_{DM}$  are in their ranges.

**4:** Allowing the ambient temperature ( $T_A$ ) to exceed the Maximum Ambient Temperature limit ( $T_{AH}$ ) may cause parameters to exceed their specified limits. See [Section 1.1 “Absolute Maximum Ratings †”](#) for the Absolute Maximum Junction Temperature and Storage Temperature limits.

**5:**  $V_{OL}$  and  $V_{OH}$  are at  $R_L = 1\text{ k}\Omega$ .

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**TABLE 1-1: VOLTAGE AND TEMPERATURE RANGES (CONTINUED)**

Parameter	Units	G <sub>DM</sub> (V/V)	Comment	Range				
				Type	Sym.	Spec.	Oper.	Abs. Min./Max.
V <sub>REF</sub>	V	All	—	Min.	V <sub>RL</sub>	0	0	-0.3
				Typ.	—	V <sub>DD</sub> /4	—	—
				Max.	V <sub>RH</sub>	V <sub>DD</sub> - 1.25	V <sub>DD</sub> - 1.15	V <sub>DD</sub> + 0.3
V <sub>OUT</sub> (Note 5)	V	All	—	Min.	V <sub>OL</sub>	0.06 Max	0	-0.3
				Typ.	—	V <sub>DD</sub> /2	—	—
				Max.	V <sub>OH</sub>	V <sub>DD</sub> - 0.13 Min	V <sub>DD</sub>	V <sub>DD</sub> + 0.3
V <sub>DM</sub>	V	20	—	Min.	V <sub>DML</sub>	-3/G <sub>DM</sub>	-4.25/G <sub>DM</sub>	-1.2
		50, 100				-4.05/G <sub>DM</sub>		
		All		Typ.	—	0	—	—
				Max.	V <sub>DMH</sub>	5.3/G <sub>DM</sub>	5.5/G <sub>DM</sub>	+1.2
T <sub>A</sub>	°C	All	—	Min.	T <sub>AL</sub>	-40	-40	-40
				Typ.	—	25	—	—
				E-Temp	Max.	T <sub>AH</sub>	+125	+150

**Note 1:** All of this table's limits are set by design and characterization.

**2:** The HV POR is triggered by V<sub>IP</sub>, with hysteresis. The LV POR is triggered by V<sub>DD</sub>, with hysteresis.

**3:** V<sub>DM</sub> = V<sub>IP</sub> - V<sub>IM</sub>. V<sub>IM</sub> is in its range when both V<sub>IP</sub> and V<sub>DM</sub> are in their ranges.

**4:** Allowing the ambient temperature (T<sub>A</sub>) to exceed the Maximum Ambient Temperature limit (T<sub>AH</sub>) may cause parameters to exceed their specified limits. See [Section 1.1 “Absolute Maximum Ratings †”](#) for the Absolute Maximum Junction Temperature and Storage Temperature limits.

**5:** V<sub>OL</sub> and V<sub>OH</sub> are at R<sub>L</sub> = 1 kΩ.

## 1.3 Specifications

**TABLE 1-2: DC ELECTRICAL CHARACTERISTICS**

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$  and  $R_L = 10\text{ k}\Omega$  to  $V_L$ ; see [Figure 1-9](#) and [Figure 1-10](#).

Parameter	Sym.	Min.	Typ.	Max.	Units	Gain	Conditions
<b>Input Offset (<math>V_{IP}</math> and <math>V_{IM}</math>) (Note 1)</b>							
Input Offset Voltage	$V_{OS}$	-16	$\pm 1.9$	+16	$\mu\text{V}$	20	Note 2
		-14	$\pm 1.65$	+14		50	
		-12	$\pm 1.5$	+12		100	
$V_{OS}$ Drift, Linear Temp. Co.	$TC_1$	-90	$\pm 10$	+90	$\text{nV}/^\circ\text{C}$	20	$T_A = -40^\circ\text{C to } +125^\circ\text{C}$ , for E-Temp parts (Note 2, Note 3)
		-70	$\pm 8$	+70		50	
		-65	$\pm 7$	+65		100	
$V_{OS}$ Drift, Quadratic Temp. Co.	$TC_2$	—	$\pm 60$	—	$\text{pV}/^\circ\text{C}^2$	20	
			$\pm 95$			50	
			$\pm 105$			100	
$V_{OS}$ Drift, Exponential Temp. Co.	$TC_X$	—	1.8	—	$\mu\text{V}$	20	
			0.31			50	
			0.10			100	
<b>Input Offset (<math>V_{IP}</math> and <math>V_{IM}</math>) – Continued (Note 1)</b>							
$V_{OS}$ Aging	$\Delta V_{OS}$	—	$\pm 0.18$	—	$\mu\text{V}$	20	108 hr at $+150^\circ\text{C}$ (changes measured at $+25^\circ\text{C}$ )
			$\pm 0.11$			50	
			$\pm 0.09$			100	
$TC_1$ Aging	$\Delta TC_1$	—	$\pm 1.9$	—	$\text{nV}/^\circ\text{C}$	20	
			$\pm 1.1$			50	
			$\pm 1.0$			100	
Power Supply Rejection Ratio	PSRR	109	134	—	dB	20	$V_{DD} = 2.0\text{V to } 5.5\text{V}$
		115	138			50	
		116	140			100	
<b>Input Current and Impedance (<math>V_{IP}</math> and <math>V_{IM}</math>)</b>							
$V_{IP}$ 's Input Bias Current	$I_{BP}$	120	170	215	$\mu\text{A}$	All	$V_{DD} = 2.0\text{V to } 5.5\text{V}$
$V_{IM}$ 's Input Bias Current	$I_{BM}$	—	$\pm 0.2$	—	nA		$V_{DD} = 5.5\text{V}$
	$I_{BM2}$		3				$V_{DD} = 5.5\text{V}$ , $V_{DM} = V_{DML}$
	$I_{BM3}$		-2				$V_{DD} = 5.5\text{V}$ , $V_{DM} = V_{DMH}$
Capacitance at $V_{IP}$	$C_{VIP}$	—	40	—	pF		
Capacitance at $V_{IM}$	$C_{VIM}$		11				
Capacitance across $V_{DM}$	$C_{VDM}$		12				

- Note 1:** The  $V_{IP}$  input is treated as the Common-mode input (e.g., for CMRR).  $V_{DM} = (V_{IP} - V_{IM})$ .
- Set by design and characterization.  $V_{OS}$  is screened in production (see [Appendix B: "Offset Test Screens"](#)).
  - See the discussion in [Section 1.6.2, Input Offset Related Errors](#).
  - See [Section 1.6, Explanation of DC Error Specifications](#).

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**TABLE 1-2: DC ELECTRICAL CHARACTERISTICS (CONTINUED)**

Electrical Characteristics: Unless otherwise indicated, $T_A = +25^\circ\text{C}$ , $V_{DD} = 2.0\text{V to } 5.5\text{V}$ , $V_{SS} = \text{GND}$ , $V_{IP} = 34\text{V}$ , $V_{DM} = 0\text{V}$ , $V_{REF} = V_{DD}/4$ , $V_L = V_{DD}/2$ and $R_L = 10\text{ k}\Omega$ to $V_L$ ; see <a href="#">Figure 1-9</a> and <a href="#">Figure 1-10</a> .							
Parameter	Sym.	Min.	Typ.	Max.	Units	Gain	Conditions
<b>Input Common-Mode Voltage (<math>V_{IP}</math>)</b>							
$V_{IP}$ 's Voltage Range Low	$V_{IPL}$	—	2.4	3.0	V	All	$V_{IP} \uparrow$
	$V_{IPLD}$		2.15	2.8			$V_{IP} \downarrow$
	$V_{IPLH}$		0.2	—			$V_{IPLH} = V_{IPL} - V_{IPLD}$
$V_{IP}$ 's Voltage Range High	$V_{IPH}$	65	—	—			
Common-Mode Rejection Ratio	CMRR	132	159	—	dB	20	$V_{DD} = 2.0\text{V to } 5.5\text{V}$ , $V_{IP} = 3\text{V to } 65\text{V}$
		138	163	50			
		165	100				
Common-Mode Nonlinearity ( <a href="#">Note 4</a> )	$INL_{CM}$	—	$\pm 0.006$	—	ppm	All	$V_{DD} = 5.5\text{V}$ , $V_{IP} = 3\text{V to } 65\text{V}$
<b>Reference Voltage (<math>V_{REF}</math>)</b>							
Reference Voltage Range ( <a href="#">Note 2</a> )	$V_{RL}$	—	—	0	V	All	See <a href="#">Section 5.1.5, Setting the Voltage at <math>V_{REF}</math></a>
	$V_{RH}$	$V_{DD} - 1.25$	—	—			
Gain Resistance	$R_F + R_G$	—	175	—	k $\Omega$	20	
			185	50			
			240	100			
$V_{REF}$ Input Capacitance	$C_{REF}$	—	11	—	pF	All	
<b>Differential Input (<math>V_{DM}</math>) (<a href="#">Note 1</a>)</b>							
Differential Gain	$G_{DM}$	20			V/V	20	MCP6C02-020
		50				50	MCP6C02-050
		100				100	MCP6C02-100
<b>Differential Input (<math>V_{DM}</math>) – Continued (<a href="#">Note 1</a>)</b>							
Differential Input Voltage Range	$V_{DML}$	$-3/G_{DM}$	—	—	V	20	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 4.1\text{V}$ , $V_L = 0\text{V}$
		$-4.05/G_{DM}$				50, 100	
	$V_{DMH}$	—		$5.3/G_{DM}$		All	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 0\text{V}$ , $V_L = V_{DD}$
Differential Gain Error	$g_E$	—	$\pm 0.1$	—	%		$V_{DD} = 2.0\text{V}$ , $V_{REF} = 0.5\text{V}$ , $G_{DM}V_{DM} = -0.4\text{V to } 1.4\text{V}$
		-1.6	$\pm 0.1$	+1.6			$V_{DD} = 5.5\text{V}$ , $V_{REF} = 2.75\text{V}$ , $G_{DM}V_{DM} = -2.65\text{V to } 2.65\text{V}$
		—	$\pm 0.1$	—			$V_{DD} = 5.5\text{V}$ , $V_{REF} = 0\text{V}$ , $G_{DM}V_{DM} = 0.2\text{V to } 5.3\text{V}$
			$\pm 0.1$			20	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 4.25\text{V}$ , $G_{DM}V_{DM} = -3\text{V to } 1.3\text{V}$
			$\pm 0.1$			50, 100	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 4.25\text{V}$ , $G_{DM}V_{DM} = -4\text{V to } 1.3\text{V}$

- Note 1:** The  $V_{IP}$  input is treated as the Common-mode input (e.g., for CMRR).  $V_{DM} = (V_{IP} - V_{IM})$ .
- Note 2:** Set by design and characterization.  $V_{OS}$  is screened in production (see [Appendix B: "Offset Test Screens"](#)).
- Note 3:** See the discussion in [Section 1.6.2, Input Offset Related Errors](#).
- Note 4:** See [Section 1.6, Explanation of DC Error Specifications](#).



**TABLE 1-2: DC ELECTRICAL CHARACTERISTICS (CONTINUED)**

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V}$  to  $5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$  and  $R_L = 10\text{ k}\Omega$  to  $V_L$ ; see [Figure 1-9](#) and [Figure 1-10](#).

Parameter	Sym.	Min.	Typ.	Max.	Units	Gain	Conditions	
Differential Gain Drift	$\Delta g_E/\Delta T_A$	—	$\pm 5$	—	ppm/ $^\circ\text{C}$	All	$V_{DD} = 2.0\text{V}$ , $V_{REF} = 0.5\text{V}$ , $G_{DM}V_{DM} = -0.4\text{V}$ to $1.4\text{V}$	
		—	$\pm 5$	—			$V_{DD} = 5.5\text{V}$ , $V_{REF} = 2.75\text{V}$ , $G_{DM}V_{DM} = -2.65\text{V}$ to $2.65\text{V}$	
$g_E$ Aging	$\Delta g_E$	—	$\pm 0.15$	—	%		408 hr at $+150^\circ\text{C}$ , $V_{DD} = 5.5\text{V}$ , $V_{REF} = 2.75\text{V}$ , $G_{DM}V_{DM} = -2.65\text{V}$ to $2.65\text{V}$ , (change measured at $+25^\circ\text{C}$ )	
Differential Nonlinearity (Note 4)	$\text{INL}_{DM}$	—	$\pm 50$	—	ppm		$V_{DD} = 2.0\text{V}$ , $V_{REF} = 0.5\text{V}$ , $G_{DM}V_{DM} = -0.4\text{V}$ to $1.4\text{V}$	
			$\pm 100$				$V_{DD} = 5.5\text{V}$ , $V_{REF} = 2.75\text{V}$ , $G_{DM}V_{DM} = -2.65\text{V}$ to $2.65\text{V}$	
<b>Output (<math>V_{OUT}</math>)</b>								
Minimum Output Voltage Swing	$V_{OL}$	—	3	—	mV	All	$V_{DD} = 2.0\text{V}$ , $V_{REF} = 0\text{V}$ , $V_{DM} = -0.5\text{V}/G_{DM}$	
			5				$V_{DD} = 5.5\text{V}$ , $V_{REF} = 0\text{V}$ , $V_{DM} = -0.5\text{V}/G_{DM}$	
			20				60	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 0\text{V}$ , $V_{DM} = -0.5\text{V}/G_{DM}$ , $R_L = 1\text{ k}\Omega$
			3				—	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 0\text{V}$ , $V_{DM} = -0.5\text{V}/G_{DM}$ , $V_L = 0\text{V}$
<b>Output (<math>V_{OUT}</math>) – Continued</b>								
Maximum Output Voltage Swing	$V_{DD} - V_{OH}$	—	6	—	mV	All	$V_{DD} = 2.0\text{V}$ , $V_{REF} = 0.75\text{V}$ , $V_{DM} = 1.75\text{V}/G_{DM}$	
			10				$V_{DD} = 5.5\text{V}$ , $V_{REF} = 4.25\text{V}$ , $V_{DM} = -1.75\text{V}/G_{DM}$	
			40				130	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 4.25\text{V}$ , $V_{DM} = 1.75\text{V}/G_{DM}$ , $R_L = 1\text{ k}\Omega$
			5				—	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 0\text{V}$ , $V_{DM} = 1.75\text{V}/G_{DM}$ , $V_L = V_{DD}$
Output Short Circuit Current	$I_{SCP}$	—	+12	—			$V_{DD} = 2.0\text{V}$ , $G_{DM}V_{DM} = 1.0\text{V}$	
			+20				$V_{DD} = 5.5\text{V}$ , $G_{DM}V_{DM} = 2.75\text{V}$	
	$I_{SCM}$		-12				—	$V_{DD} = 2.0\text{V}$ , $G_{DM}V_{DM} = 0\text{V}$
			-20					$V_{DD} = 5.5\text{V}$ , $G_{DM}V_{DM} = 0\text{V}$
<b>Power Supplies (<math>V_{DD}</math>, <math>V_{SS}</math> and <math>V_{IP}</math>)</b>								
Low Supply Voltage	$V_{DD}$	2.0	—	5.5	V	All	$I_O = 0\text{A}$	
High Supply Voltage	$V_{IP}$	(see $V_{IP}$ spec)						
Quiescent Current at $V_{SS}$	$I_{SS}$	—	-660	—	$\mu\text{A}$			
Quiescent Current at $V_{DD}$	$I_{DD}$	300	490	725				
Quiescent Current at $V_{IP}$	$I_{BP}$	(see $I_{BP}$ spec)						

- Note 1:** The  $V_{IP}$  input is treated as the Common-mode input (e.g., for CMRR).  $V_{DM} = (V_{IP} - V_{IM})$ .
- 2:** Set by design and characterization.  $V_{OS}$  is screened in production (see [Appendix B: “Offset Test Screens”](#)).
- 3:** See the discussion in [Section 1.6.2, Input Offset Related Errors](#).
- 4:** See [Section 1.6, Explanation of DC Error Specifications](#).

# MCP6C02

**TABLE 1-2: DC ELECTRICAL CHARACTERISTICS (CONTINUED)**

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$  and  $R_L = 10\text{ k}\Omega$  to  $V_L$ ; see [Figure 1-9](#) and [Figure 1-10](#).

Parameter	Sym.	Min.	Typ.	Max.	Units	Gain	Conditions
POR Trip Voltages, Low-Side ( $V_{DD}$ )	$V_{PLL}$	1.05	1.35	—	V	All	LV POR turns off ( $V_{DD} \downarrow$ ), $V_L = 0\text{V}$ , $V_{IP} = 3\text{V}$ , $V_{REF} = 0\text{V}$
	$V_{PLH}$	—	1.45	1.7			LV POR turns on ( $V_{DD} \uparrow$ ), $V_L = 0\text{V}$ , $V_{IP} = 3\text{V}$ , $V_{REF} = 0\text{V}$
POR Trip Voltages, High-Side ( $V_{IP}$ )	$V_{PHL}$	1.7	1.95	—			HV POR turns off ( $V_{IP} \downarrow$ ), $R_L = \text{open}$ , $V_{DD} = 5.5\text{V}$ (change in $I_{SS}$ )
	$V_{PHH}$	—	2.05	2.6			HV POR turns on ( $V_{IP} \uparrow$ ), $R_L = \text{open}$ , $V_{DD} = 5.5\text{V}$ (change in $I_{SS}$ )

- Note 1:** The  $V_{IP}$  input is treated as the Common-mode input (e.g., for CMRR).  $V_{DM} = (V_{IP} - V_{IM})$ .
- Note 2:** Set by design and characterization.  $V_{OS}$  is screened in production (see [Appendix B: "Offset Test Screens"](#)).
- Note 3:** See the discussion in [Section 1.6.2, Input Offset Related Errors](#).
- Note 4:** See [Section 1.6, Explanation of DC Error Specifications](#).

**TABLE 1-3: AC ELECTRICAL CHARACTERISTICS**

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-11](#).

Parameter	Sym.	Min.	Typ.	Max.	Units	Gain	Conditions
<b>AC Response</b>							
Bandwidth	BW	—	500	—	kHz	20, 50	$G_{DM}V_{DM} = 0.1V_{p-p}$
			390				
Gain Peaking	GPK	—	0	—	dB	All	
<b>Step Response</b>							
$V_{DM}$ Slew Rate	SR	(Note 1)			$V/\mu\text{s}$	All	$G_{DM}V_{DM} \text{ Step} = V_{DD} - 0.5\text{V}$
$V_{DM}$ Step Overshoot	$OS_{DM}$	—	4	—	%		$G_{DM}V_{DM} \text{ Step} = 0.1\text{V}$ , $t_{r\_in} = 0.2\text{ }\mu\text{s}$
Overdrive Recovery, Input Differential Mode	$t_{IRDL}$	—	3	—	$\mu\text{s}$	20	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 4\text{V}$ , $G_{DM}V_{DM} = -3.5\text{V to } -1.25\text{V Step}$ , 90% of $V_{OUT}$ change
							(see $t_{ORL}$ Spec)
	$t_{IRDH}$	—	3	—		All	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 0.5\text{V}$ , $G_{DM}V_{DM} = +4.5\text{V to } +2.25\text{V Step}$ , 90% of $V_{OUT}$ change

- Note 1:** SR is limited by GBWP; the large signal step response is dominated by the small signal bandwidth.
- Note 2:** At these gains, we cannot distinguish between overdriving  $V_{DM}$  or  $V_{OUT}$ .
- Note 3:** See [Figure 2-57](#) for the noise density over a wider frequency range.

**TABLE 1-3: AC ELECTRICAL CHARACTERISTICS (CONTINUED)**

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-11](#).

Parameter	Sym.	Min.	Typ.	Max.	Units	Gain	Conditions
Overdrive Recovery, Output	$t_{ORL}$	—	1.5	—	$\mu\text{s}$	All	$V_{DD} = 2.0\text{V}$ , $V_{REF} = 0\text{V}$ , $G_{DM}V_{DM} = -0.5\text{V to } +1\text{V Step}$ , 90% of $V_{OUT}$ change
			1.5				$V_{DD} = 5.5\text{V}$ , $V_{REF} = 0\text{V}$ , $G_{DM}V_{DM} = -0.5\text{V to } +2.75\text{V Step}$ , 90% of $V_{OUT}$ change
	$t_{ORH}$	—	1.5	$V_{DD} = 2.0\text{V}$ , $V_{REF} = 0.6\text{V}$ , $G_{DM}V_{DM} = +1.9\text{V to } +0.4\text{V Step}$ , 90% of $V_{OUT}$ change			
			1.5	$V_{DD} = 5.5\text{V}$ , $V_{REF} = 4.1\text{V}$ , $G_{DM}V_{DM} = +1.9\text{V to } -1.35\text{V Step}$ , 90% of $V_{OUT}$ change			
<b>Noise</b>							
Input Noise Voltage	$E_{ni}$	—	0.48	—	$\mu\text{V}_{p-p}$	20	$f = 0.01\text{ Hz to } 1\text{ Hz}$
			0.30				
			0.29				
			1.54				$f = 0.1\text{ Hz to } 10\text{ Hz}$
			0.95				
			0.92				
Input Noise Voltage Density ( <a href="#">Note 3</a> )	$e_{ni}$	—	74	—	nV/√Hz	20	$f < 500\text{ Hz}$
			46				50
			44				100
Input Current Noise Density – At $V_{IP}$	$i_{nip}$	—	10	—	pA/√Hz	All	$f = 1\text{ kHz}$
Input Current Noise Density – At $V_{IM}$	$i_{nim}$	—	8	—	fA/√Hz	All	$f = 1\text{ kHz}$ , $V_{DM} = 0\text{V}$
			33				$f = 1\text{ kHz}$ , $V_{DM} = 0.15\text{V}$
<b>EMI Protection</b>							
EMI Rejection Ratio	EMIRR	—	96	—	dB	All	$V_{IN} = 0.1\text{V}_{PK}$ , $f = 400\text{ MHz}$
			91				$V_{IN} = 0.1\text{V}_{PK}$ , $f = 900\text{ MHz}$
			114				$V_{IN} = 0.1\text{V}_{PK}$ , $f = 1800\text{ MHz}$
			118				$V_{IN} = 0.1\text{V}_{PK}$ , $f = 2400\text{ MHz}$
			121				$V_{IN} = 0.1\text{V}_{PK}$ , $f = 6000\text{ MHz}$
<b>Power Up/Down</b>							
Power On Time ( $V_{DD} \uparrow$ ), $V_{OUT}$ Settles	$t_{PON}$	—	65	—	$\mu\text{s}$	All	$V_{DD} = 0\text{V to } 2.0\text{V}$ , $V_L = 0\text{V}$ , 90% of $V_{OUT}$ change
			140				$V_{DD} = 0\text{V to } 5.5\text{V}$ , $V_L = 0\text{V}$ , 90% of $V_{OUT}$ change
Power Off Time ( $V_{DD} \downarrow$ ), $V_{OUT}$ Settles	$t_{POFF}$	—	8	—	$\mu\text{s}$	All	$V_{DD} = 2.0\text{V to } 0\text{V}$ , $V_L = 0\text{V}$ , 90% of $V_{OUT}$ change
			5.5				$V_{DD} = 5.5\text{V to } 0\text{V}$ , $V_L = 0\text{V}$ , 90% of $V_{OUT}$ change

- Note 1:** SR is limited by GBWP; the large signal step response is dominated by the small signal bandwidth.
- 2:** At these gains, we cannot distinguish between overdriving  $V_{DM}$  or  $V_{OUT}$ .
- 3:** See [Figure 2-57](#) for the noise density over a wider frequency range.

# MCP6C02

**TABLE 1-4: TEMPERATURE SPECIFICATIONS**

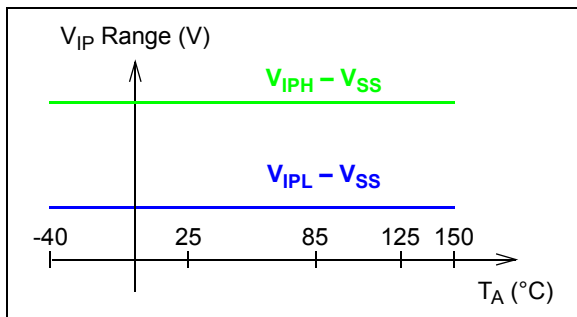
Electrical Characteristics: Unless otherwise indicated, $T_A = +25^\circ\text{C}$ , $V_{DD} = 2.0\text{V}$ to $5.5\text{V}$ , $V_{SS} = \text{GND}$ and $V_{IP} = 34\text{V}$ .						
Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
Specified Temperature Range	$T_A$	-40	—	+125	°C	
Operating Temperature Range		-40	—	+150		Note 1
Storage Temperature Range		-60	—	+150		No power
Thermal Resistance, 6L-SOT-23	$\theta_{JA}$	—	191	—	°C/W	

**Note 1:** Operation must not cause  $T_J$  to exceed the Absolute Maximum Junction Temperature specification, which is  $155^\circ\text{C}$ . See [Section 4.1.5, Temperature Performance](#) for design tips.

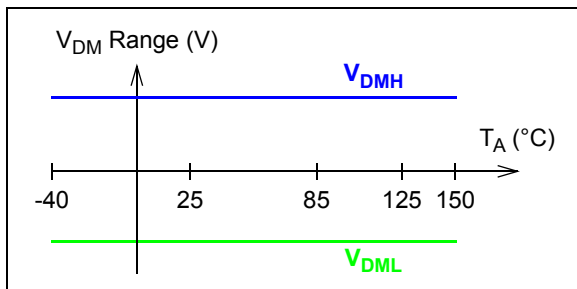
## 1.4 Simplified Diagrams

### 1.4.1 VOLTAGE RANGE DIAGRAMS

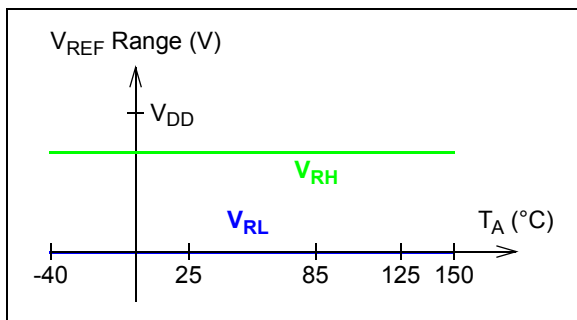
These ranges are constant across temperature.



**FIGURE 1-1:** Common-Mode Input Voltage Range vs. Temperature.

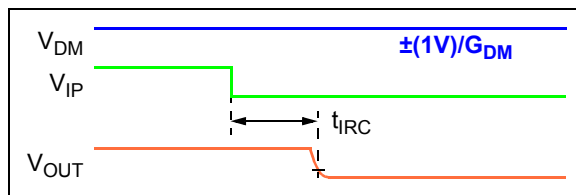


**FIGURE 1-2:** Differential Input Voltage Range vs. Temperature.

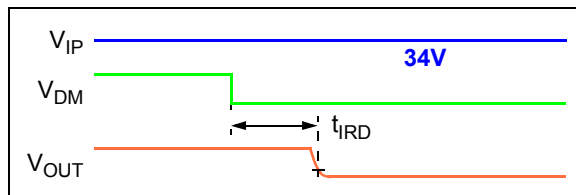


**FIGURE 1-3:** Reference Voltage Range vs. Temperature.

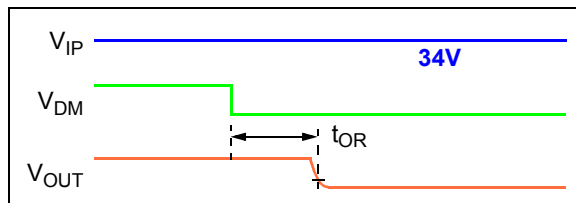
### 1.4.2 TIMING DIAGRAMS



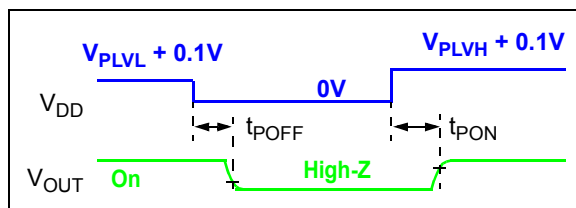
**FIGURE 1-4:** Common-Mode Input Overdrive Recovery Timing Diagram.



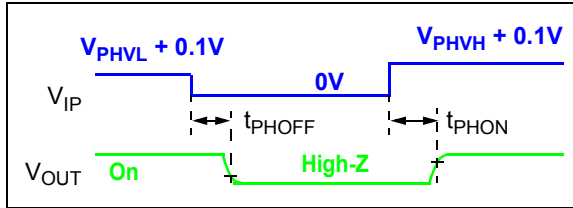
**FIGURE 1-5:** Differential-Mode Input Overdrive Recovery Timing Diagram.



**FIGURE 1-6:** Output Overdrive Recovery Timing Diagram.



**FIGURE 1-7:**  $V_{OUT}$  Power On/Off Timing Diagram, Low-Side.

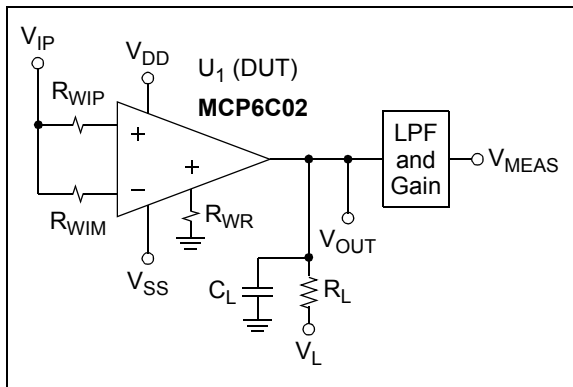


**FIGURE 1-8:**  $V_{OUT}$  Power On/Off Timing Diagram, High-Side.

## 1.5 Simplified Test Circuits

### 1.5.1 $V_{OS}$ TEST CIRCUIT

Figure 1-9 tests the MCP6C02's input offset errors ( $V_{OS}$ ,  $1/CMRR$ ,  $1/CMRR2$  and  $1/PSRR$ , etc.).  $R_{WIP}$  is set very low, so  $I_{BP}$  does not affect the result.  $V_{OUT}$  is filtered and amplified, before measuring the result.



**FIGURE 1-9:** Input Offset Test Circuit for the MCP6C02.

When MCP6C02 is in its normal range of operation, the DC output voltages are ( $V_E$  is the sum of input offset errors and  $g_E$  is the gain error):

#### EQUATION 1-1:

$$G_{DM} = DM \text{ Gain}$$

$$V_{OUT} = G_{DM}(1 + g_E)V_E + V_{REF}$$

$$V_{MEAS} = G_{PA}V_{OUT}$$

The resistances at the Device Under Test (DUT) need to be small enough for accuracy (see Figure 1-10). These resistances include wires, traces, vias, etc.

#### EQUATION 1-2:

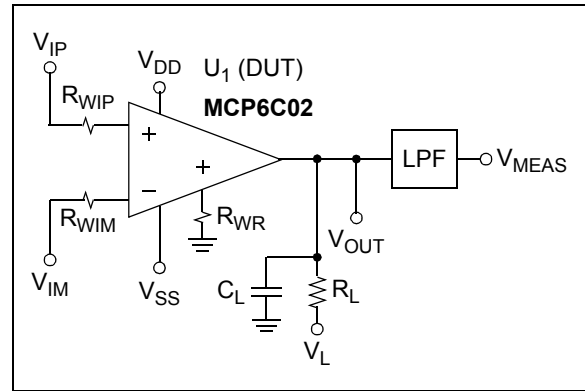
$$R_{WIP} \leq 4 \text{ m}\Omega$$

$$R_{WIM} \leq 0.1 \Omega$$

$$R_{WR} \leq 1 \Omega$$

### 1.5.2 DC DIFFERENTIAL GAIN TEST CIRCUIT

Figure 1-10 is used for testing the differential gain error, nonlinearity and input voltage range ( $g_E$ ,  $INL_{DM}$ ,  $V_{DML}$  and  $V_{DMH}$ ). We compare  $V_{MEAS}$  with the ideal  $V_{OUT}$ , then extract the above parameters.



**FIGURE 1-10:** Differential Gain Test Circuit.

When measuring the differential input range, all of the voltages must be in range except  $V_{DM}$ .

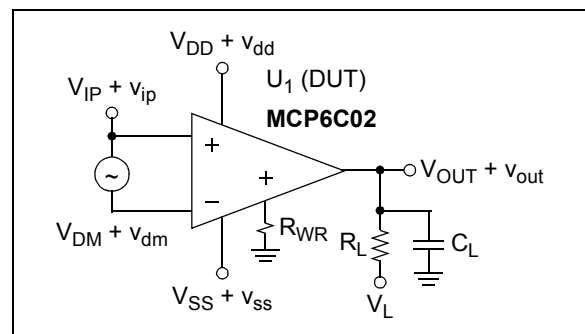
When measuring differential errors ( $g_E$ ,  $\Delta g_E/\Delta T_A$  and  $INL_{DM}$ ), all voltages are held constant, except  $V_{DM}$ .

For accuracy, the wiring resistances at the DUT need to be very small (see Equation 1-2).

### 1.5.3 AC GAINS TEST CIRCUIT

Figure 1-11 is used for testing the INA's different AC gains. The AC voltages are:

- $v_{out}$  is the AC output
- $v_{ip}$  is the AC Common-mode input, used for CMRR plots
- $v_{dm}$  is the AC differential input, used for  $G_{DM}$  plots (also for CMRR and PSRR)
- $v_{dd}$  and  $v_{ss}$  are the AC supply inputs, used for PSRR plots (including PSRR+ and PSRR-)



**FIGURE 1-11:** AC Gain Test Circuit.

The impedance at  $V_{REF}$  (shown here as  $R_{WR}$ ) needs to have a magnitude less than  $1 \Omega$ , for gain accuracy in the signal bandwidth. The magnitude needs to be  $< 50 \Omega$ , when  $f < 1 \text{ MHz}$ , to maintain good stability.

# MCP6C02

## 1.6 Explanation of DC Error Specifications

### 1.6.1 LINEAR RESPONSE MODEL

When the inputs and the output are in their normal ranges, and the nonlinear errors are negligible, the output voltage ( $V_{OUT}$ ) is:

#### EQUATION 1-3:

$$V_{OUT} = V_{REF} + G_{DM}(I + g_E)(V_{DM} + V_E)$$

$V_{DM}$  is the input voltage.  $V_E$  is the sum of input offset errors (due to  $V_{OS}$ , PSRR, CMRR, CMRR2,  $TC_1$ ,  $TC_2$ , etc.).  $g_E$  is the gain error ( $G_{DM}$  is the nominal gain).

### 1.6.2 INPUT OFFSET RELATED ERRORS

When  $V_{DM} = 0V$ , the linear response model for  $V_{OUT}$  becomes:

#### EQUATION 1-4:

$$V_{OUT} = V_{REF} + G_{DM}(I + g_E)V_E$$

The input offset error ( $V_E$ ) is extracted from input offset measurements (see [Section 1.5.1 "VOS Test Circuit"](#)):

#### EQUATION 1-6:

$$V_E = V_{OS} + \frac{\Delta V_{DD} - \Delta V_{SS}}{PSRR} + \frac{\Delta V_{IP}}{CMRR} + \frac{\Delta V_{REF}}{CMRR2} + \Delta T_A TC_1 + \Delta T_A^2 TC_2 + TC_X^2 \quad ((T_A - 150^\circ C)/(10^\circ C))$$

Where:

PSRR, CMRR and CMRR2 are in units of V/V

$\Delta T_A$  is in units of  $^\circ C$

$V_{DM} = 0$

### 1.6.3 INPUT OFFSET'S COMMON-MODE VOLTAGE NONLINEARITY

The input offset error ( $V_E$ ) changes nonlinearly with  $V_{IP}$ . [Figure 1-12](#) shows the MCP6C02's  $V_E$  vs.  $V_{IP}$ , as well as a linear fit line ( $V_{E\_LIN}$ ), that goes through the center point ( $V_C$ ,  $V_2$ ) and has the same slope as the end points.

#### EQUATION 1-5:

$$V_E = \frac{V_{OUT} - V_{REF}}{G_{DM}(I + g_E)}$$

We usually assume  $g_E = 0$ , in [Equation 1-5](#), when extracting  $V_E$ . The result is accurate enough, since  $g_E$  is so low.

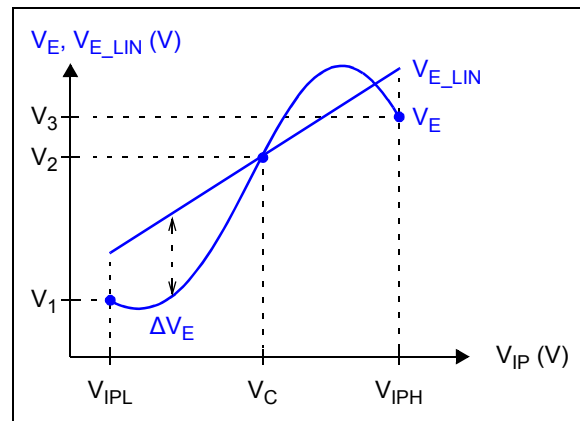
$V_E$  has several terms, which assume a linear response to changes in  $V_{DD}$ ,  $V_{SS}$ ,  $V_{IP}$  and  $V_{REF}$ .

$V_{OS}$ 's dependence on temperature ( $T_A$ ) is quadratic plus exponential ( $V_{OS}$ ,  $TC_1$ ,  $TC_2$  and  $TC_X$ ). The aging specs ( $\Delta V_{OS}$  and  $\Delta TC_1$ ) are not included, for simplicity.

The exponential factor in [Equation 1-6](#) decreases at colder temperatures ( $T_A$ ). This table gives an indication of this relationship.

**TABLE 1-5: EXPONENTIAL TERM**

$T_A$ ( $^\circ C$ )	$2^{((T_A - 150^\circ C)/(10^\circ C))}$
$\leq 65$	$\leq 0.003$
+85	0.011
+105	0.044
+125	0.177
+150	1.000



**FIGURE 1-12:** Input Offset Error vs. Common-Mode Input Voltage.

The part is in standard conditions ( $\Delta V_{OUT} = 0$ ,  $V_{DM} = 0$ , etc.).  $V_{IP}$  sweeps from  $V_{IPL}$  to  $V_{IPH}$ . The test circuit is in [Section 1.5.1, VOS Test Circuit](#). Calculate  $V_E$  at each point with [Equation 1-5](#).

Based on the measured  $V_E$  data, we obtain the following linear fit:

### EQUATION 1-7:

$$V_{E\_LIN} = V_2 + (V_{IP} - V_C) / CMRR$$

Where:

$$V_C = (V_{IPL} + V_{IPH}) / 2$$

$$1 / CMRR = (V_3 - V_1) / (V_{IPH} - V_{IPL})$$

The remaining error ( $\Delta V_E$ ) is described by the Common-mode Nonlinearity spec:

### EQUATION 1-8:

$$INL_{CMH} = \max(\Delta V_E) / (V_{IPH} - V_{IPL})$$

$$INL_{CML} = \min(\Delta V_E) / (V_{IPH} - V_{IPL})$$

$$INL_{CM} = INL_{CMH}, \quad |INL_{CMH}| \geq |INL_{CML}|$$

$$= INL_{CML}, \quad \text{otherwise}$$

Where:

$$\Delta V_E = V_E - V_{E\_LIN}$$

## 1.6.4 DIFFERENTIAL GAIN ERROR AND NONLINEARITY

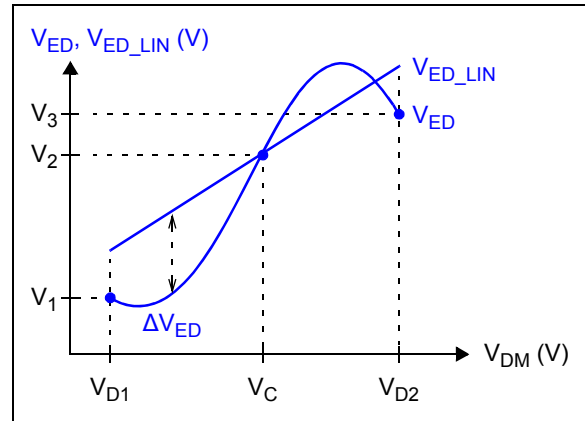
The differential errors are extracted from differential gain measurements (see [Section 1.5.2, DC Differential Gain Test Circuit](#)), based on [Equation 1-3](#). These errors are then split into the differential gain error ( $g_E$ ) and the input nonlinearity error  $INL_{DM}$ .

The error  $V_{ED}$  is calculated by subtracting the ideal output from  $V_{OUT}$ , then dividing by the ideal gain  $G_{DM}$ .

### EQUATION 1-9:

$$V_{ED} = (V_{OUT} - (V_{REF} + G_{DM} \cdot V_{DM})) / G_{DM}$$

[Figure 1-13](#) shows  $V_{ED}$  vs.  $V_{DM}$ , as well as a linear fit line ( $V_{ED\_LIN}$ ) based on  $V_{DM}$  and  $g_E$ . The amplifier is in one of the standard condition sets. The linear fit line ( $V_{ED\_LIN}$ ) goes through the center point ( $V_C$ ,  $V_2$ ) and has the same slope as the end points.



**FIGURE 1-13:** Differential Input Error vs. Differential Input Voltage.

Based on the measured  $V_{ED}$  data, we obtain the following linear fit:

### EQUATION 1-10:

$$V_{ED\_LIN} = V_2 + (V_{DM} - V_C) g_E$$

Where:

$$V_C = (V_{D1} + V_{D2}) / 2$$

$$g_E = (V_3 - V_1) / (V_{D2} - V_{D1})$$

The remaining error ( $\Delta V_{ED}$ ) is described by the Differential Nonlinearity spec:

### EQUATION 1-11:

$$INL_{DMH} = \max(\Delta V_{ED}) / (V_{D2} - V_{D1})$$

$$INL_{DML} = \min(\Delta V_{ED}) / (V_{D2} - V_{D1})$$

$$INL_{DM} = INL_{DMH}, \quad |INL_{DMH}| \geq |INL_{DML}|$$

$$= INL_{DML}, \quad \text{otherwise}$$

Where:

$$\Delta V_{ED} = V_{ED} - V_{ED\_LIN}$$

The aging spec  $\Delta g_E$  is not included here, for simplicity.  $V_{DM}$  sweeps are not always centered on  $V_{DM} = 0V$ ; the  $INL_{DM}$  spec will interact with the  $V_{OS}$  spec.

# MCP6C02

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NOTES:

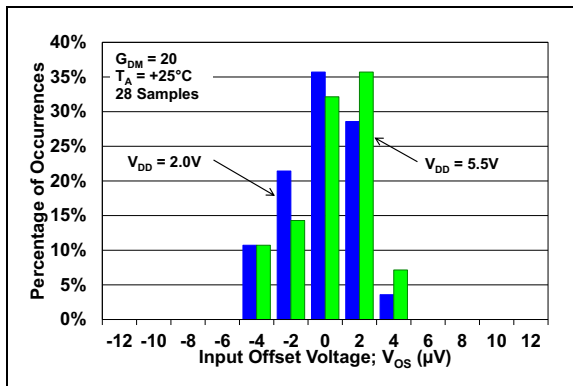


## 2.0 TYPICAL PERFORMANCE CURVES

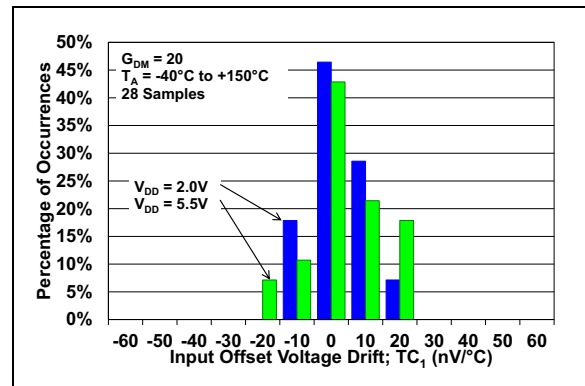
**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V}$  to  $5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see Figure 1-9, Figure 1-10 and Figure 1-11.

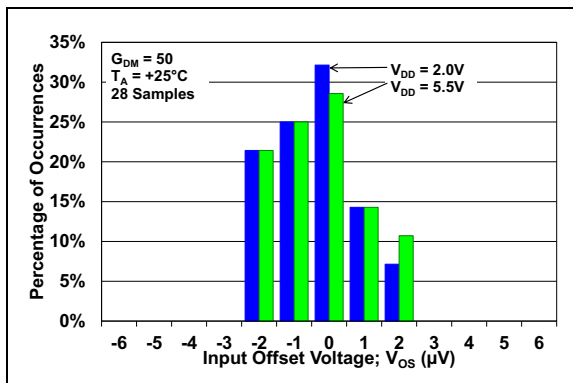
### 2.1 DC Precision



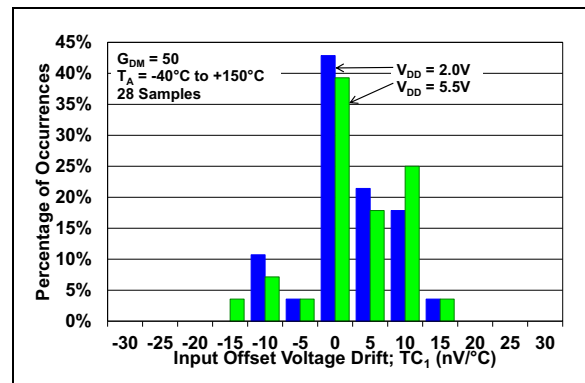
**FIGURE 2-1:** Input Offset Voltage,  $G_{DM} = 20$ .



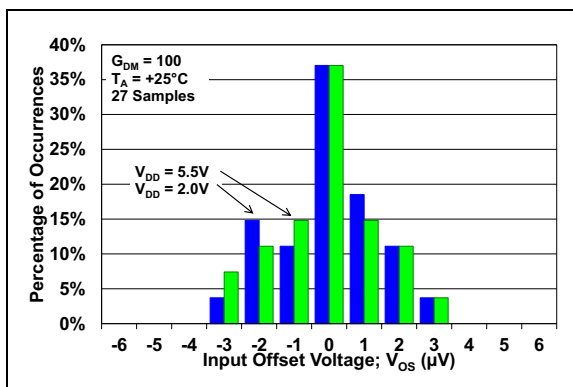
**FIGURE 2-4:** Linear Input Offset Voltage Drift,  $G_{DM} = 20$ .



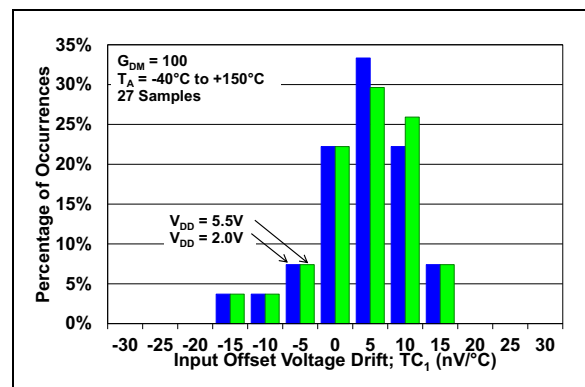
**FIGURE 2-2:** Input Offset Voltage,  $G_{DM} = 50$ .



**FIGURE 2-5:** Linear Input Offset Voltage Drift,  $G_{DM} = 50$ .



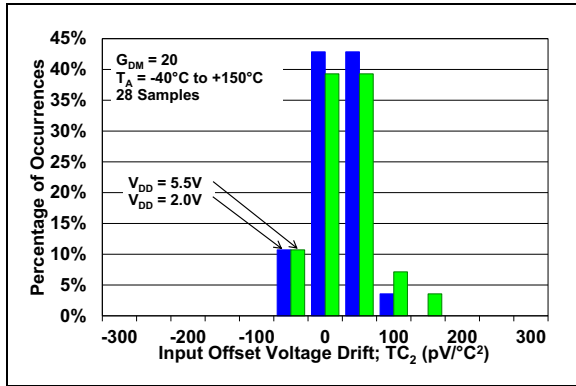
**FIGURE 2-3:** Input Offset Voltage,  $G_{DM} = 100$ .



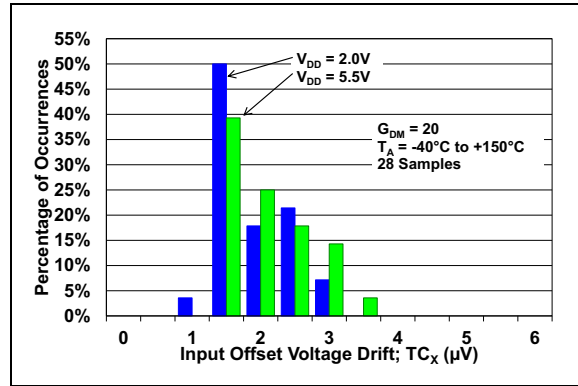
**FIGURE 2-6:** Linear Input Offset Voltage Drift,  $G_{DM} = 100$ .

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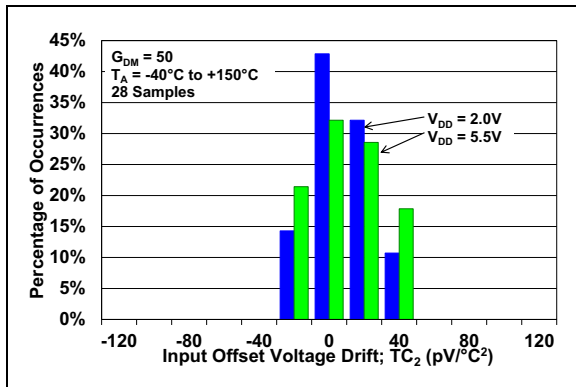
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V}$  to  $5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).



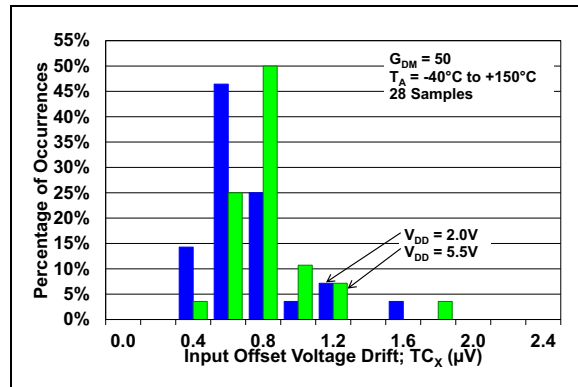
**FIGURE 2-7:** Quadratic Input Offset Voltage Drift,  $G_{DM} = 20$ .



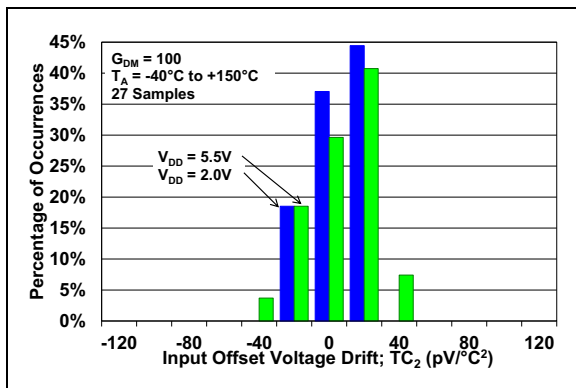
**FIGURE 2-10:** Exponential Input Offset Voltage Drift,  $G_{DM} = 20$ .



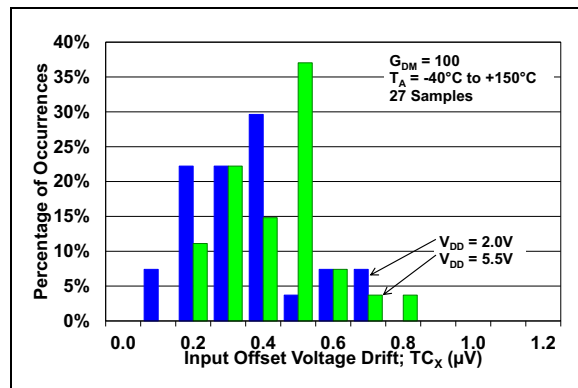
**FIGURE 2-8:** Quadratic Input Offset Voltage Drift,  $G_{DM} = 50$ .



**FIGURE 2-11:** Exponential Input Offset Voltage Drift,  $G_{DM} = 50$ .

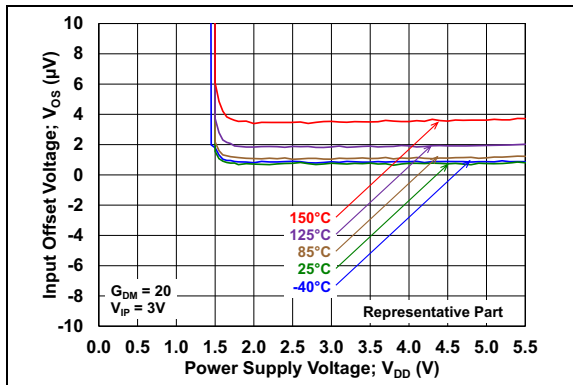


**FIGURE 2-9:** Quadratic Input Offset Voltage Drift,  $G_{DM} = 100$ .

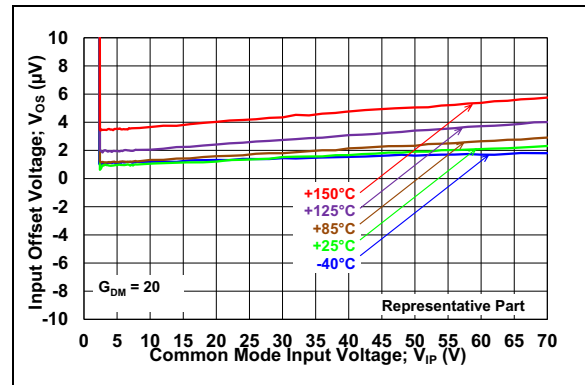


**FIGURE 2-12:** Exponential Input Offset Voltage Drift,  $G_{DM} = 100$ .

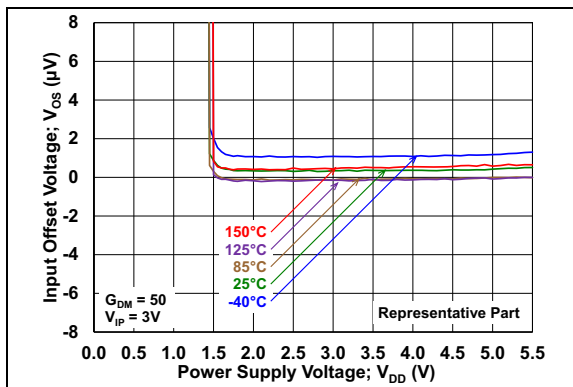
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).



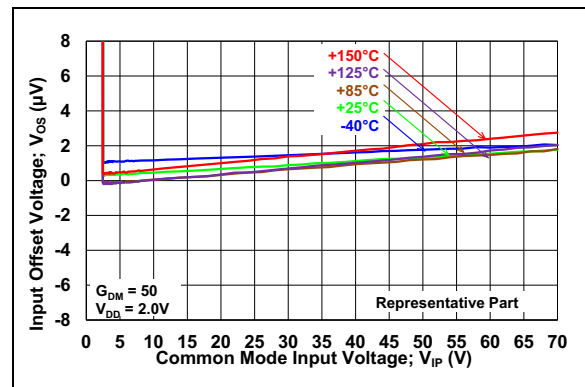
**FIGURE 2-13:** Input Offset Voltage vs. Power Supply Voltage, with  $G_{DM} = 20$ .



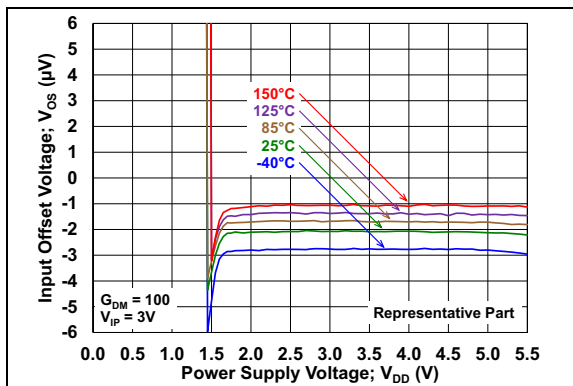
**FIGURE 2-16:** Input Offset Voltage vs. Common-Mode Input Voltage, with  $G_{DM} = 20$ .



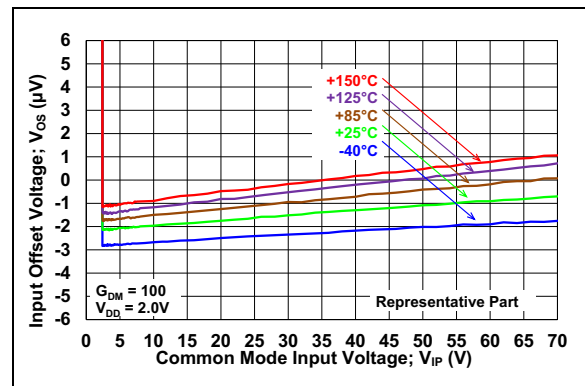
**FIGURE 2-14:** Input Offset Voltage vs. Power Supply Voltage, with  $G_{DM} = 50$ .



**FIGURE 2-17:** Input Offset Voltage vs. Common-Mode Input Voltage, with  $G_{DM} = 50$ .



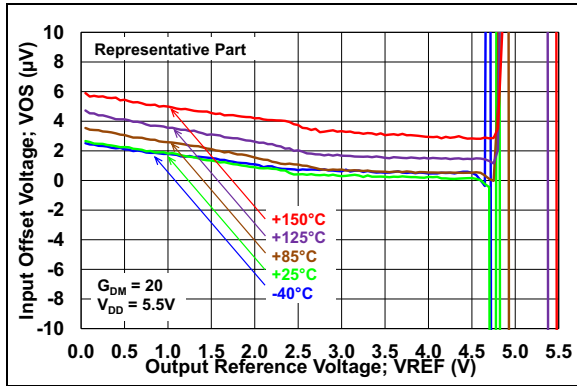
**FIGURE 2-15:** Input Offset Voltage vs. Power Supply Voltage, with  $G_{DM} = 100$ .



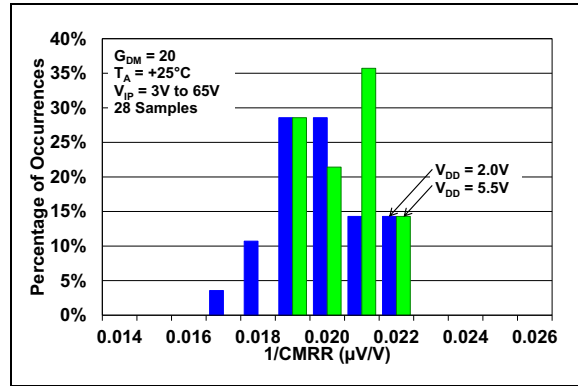
**FIGURE 2-18:** Input Offset Voltage vs. Common-Mode Input Voltage, with  $G_{DM} = 100$ .

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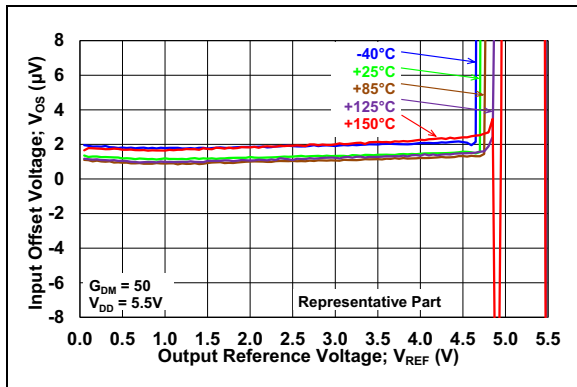
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).



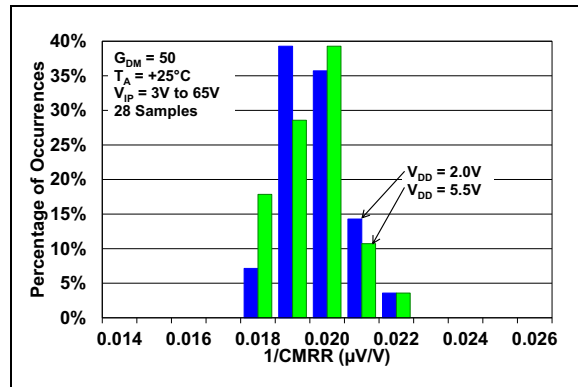
**FIGURE 2-19:** Input Offset Voltage vs. Reference Voltage, with  $G_{DM} = 20$ .



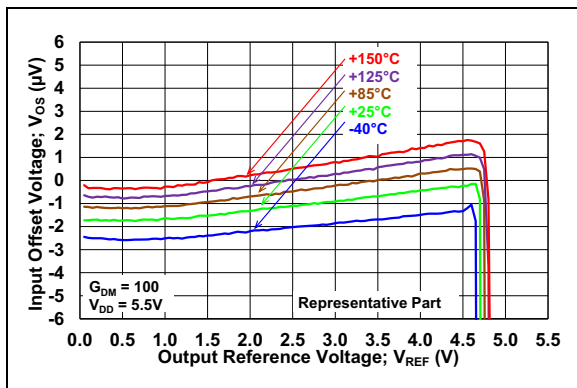
**FIGURE 2-22:**  $1/\text{CMRR}$ , with  $G_{DM} = 20$ .



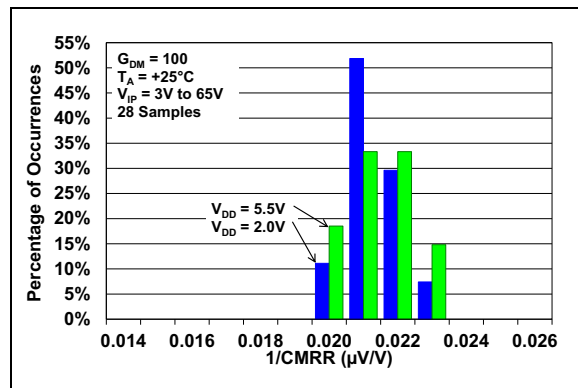
**FIGURE 2-20:** Input Offset Voltage vs. Reference Voltage, with  $G_{DM} = 50$ .



**FIGURE 2-23:**  $1/\text{CMRR}$ , with  $G_{DM} = 50$ .

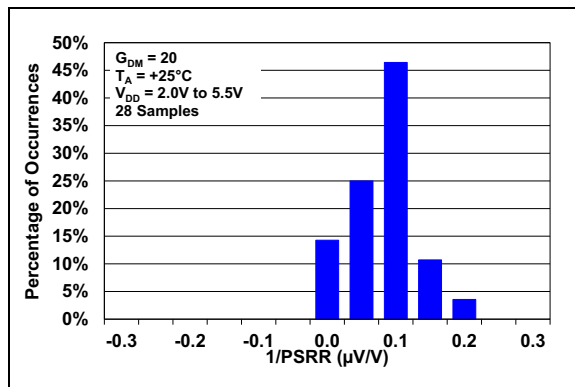


**FIGURE 2-21:** Input Offset Voltage vs. Reference Voltage, with  $G_{DM} = 100$ .

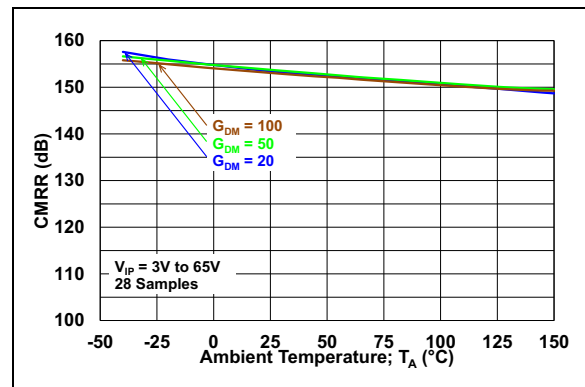


**FIGURE 2-24:**  $1/\text{CMRR}$ , with  $G_{DM} = 100$ .

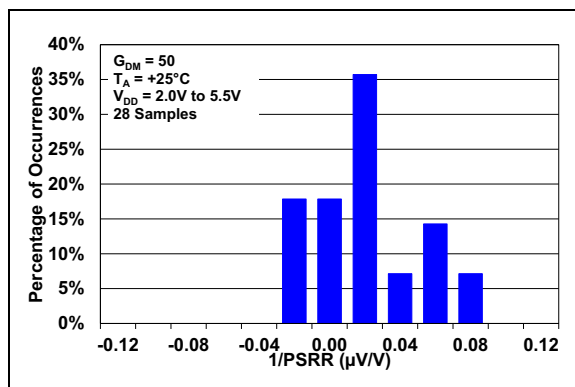
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see Figure 1-9, Figure 1-10 and Figure 1-11.



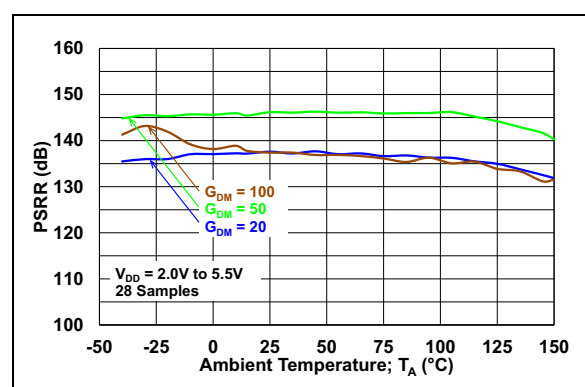
**FIGURE 2-25:**  $1/PSRR$ , with  $G_{DM} = 20$ .



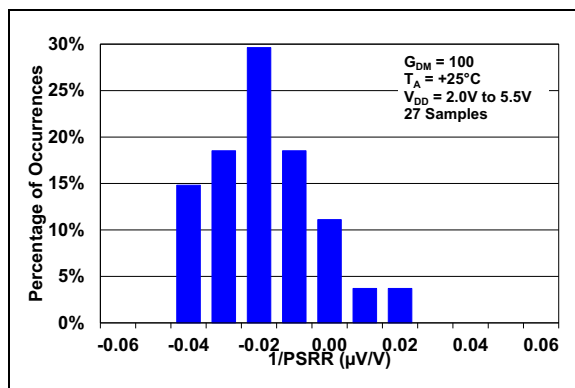
**FIGURE 2-28:**  $CMRR$  vs. Ambient Temperature.



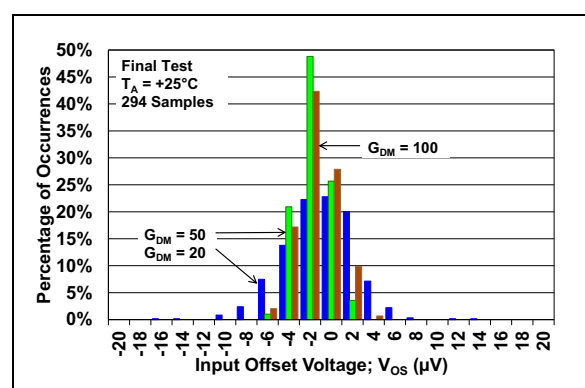
**FIGURE 2-26:**  $1/PSRR$ , with  $G_{DM} = 50$ .



**FIGURE 2-29:**  $PSRR$  vs. Ambient Temperature.



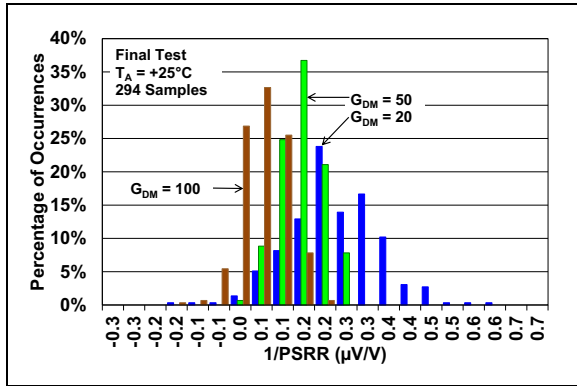
**FIGURE 2-27:**  $1/PSRR$ , with  $G_{DM} = 100$ .



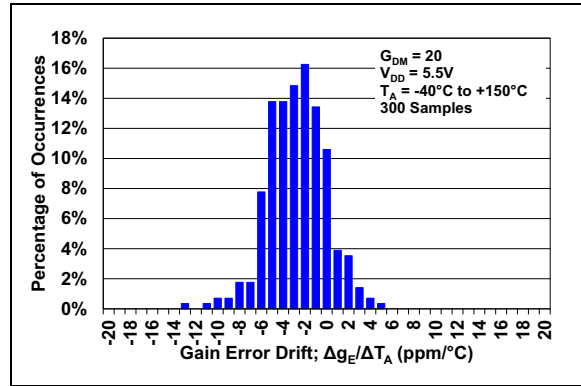
**FIGURE 2-30:** Input Offset Voltage - Final Test Results.

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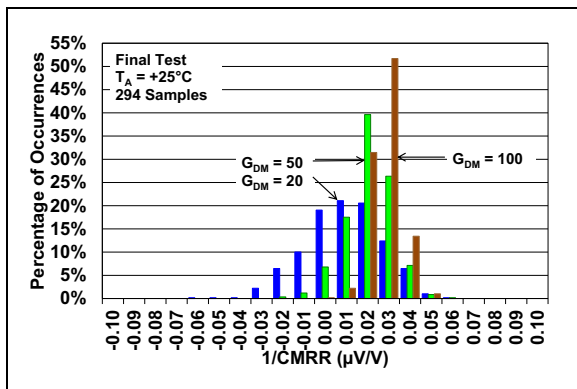
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V}$  to  $5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).



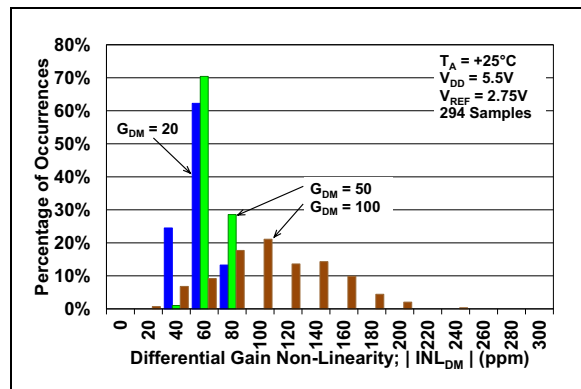
**FIGURE 2-31:** PSRR - Final Test Results.



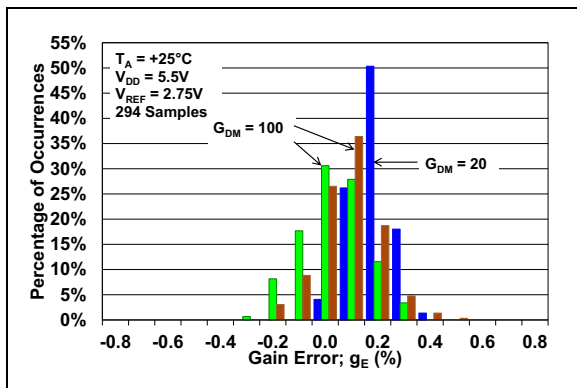
**FIGURE 2-34:** Gain Error Temperature Drift.



**FIGURE 2-32:** CMRR - Final Test Results.



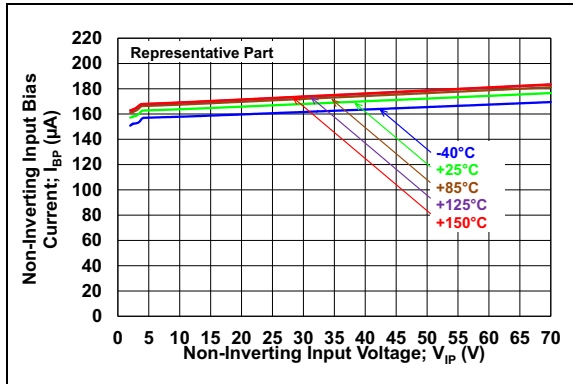
**FIGURE 2-35:** Differential Gain Nonlinearity.



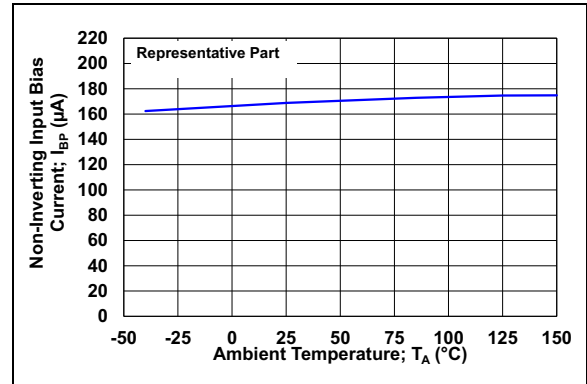
**FIGURE 2-33:** Gain Error.

**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).

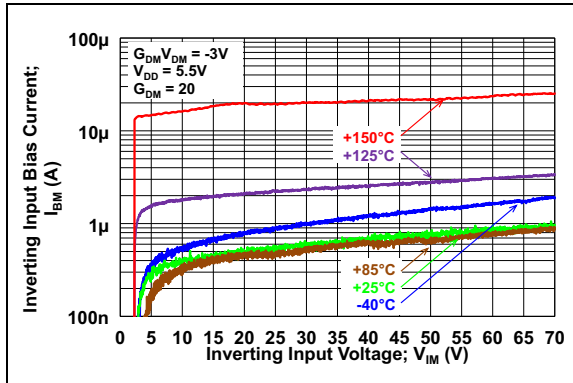
## 2.2 Other DC Voltages and Currents



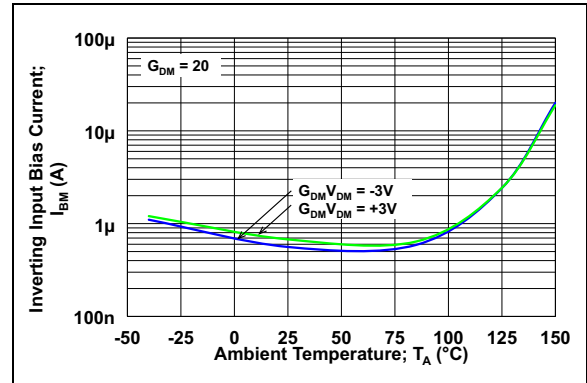
**FIGURE 2-36:**  $V_{IP}$  Pin Input Bias Current vs. Input Common-Mode Voltage.



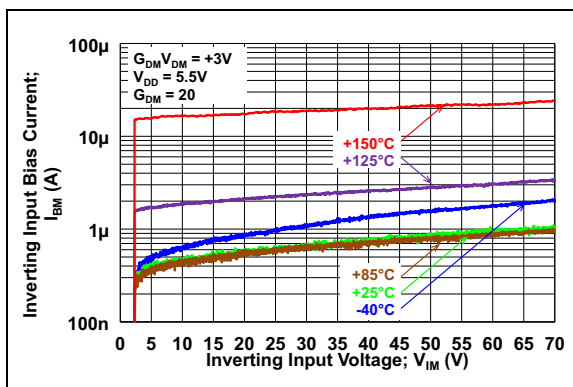
**FIGURE 2-39:**  $V_{IP}$  Pin Input Bias Current vs. Ambient Temperature.



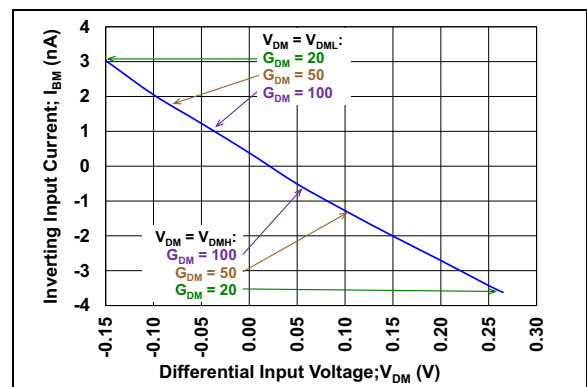
**FIGURE 2-37:**  $V_{IM}$  Pin Input Bias Current vs. Input Common-Mode Voltage,  $V_{DM} = V_{DML}$ .



**FIGURE 2-40:**  $V_{IM}$  Pin Input Bias Current vs. Ambient Temperature.



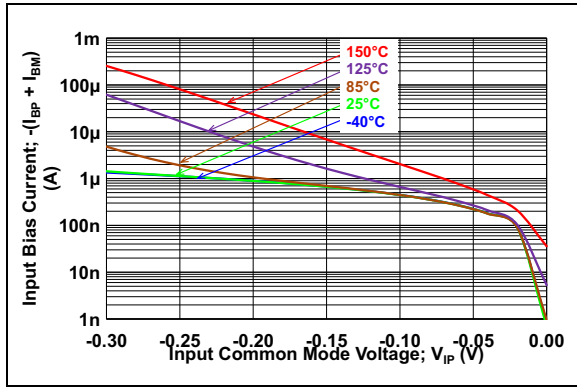
**FIGURE 2-38:**  $V_{IM}$  Pin Input Bias Current vs. Input Common-Mode Voltage,  $V_{DM} = V_{DMH}$ .



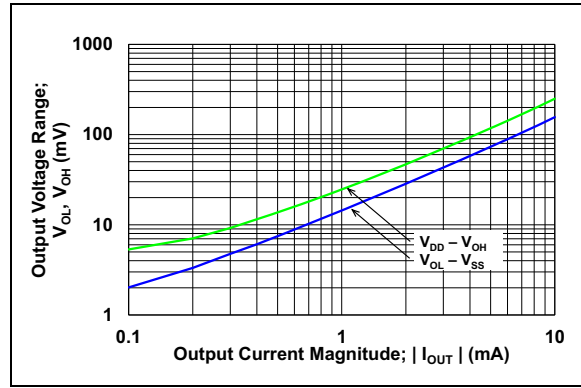
**FIGURE 2-41:**  $V_{IM}$  Pin Input Bias Current vs. Differential Input Voltage.

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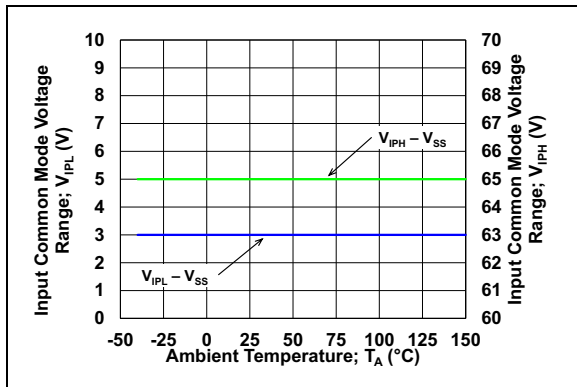
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V}$  to  $5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).



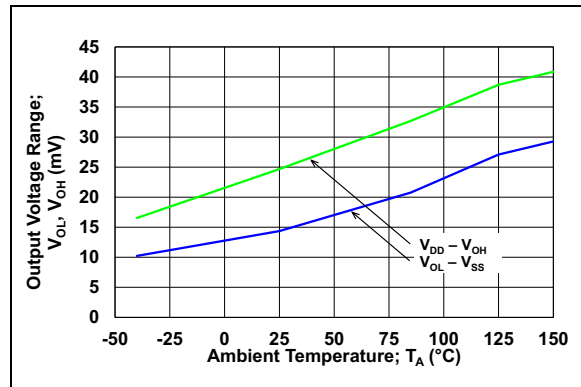
**FIGURE 2-42:** Input Bias Current vs. Input Common-Mode Voltage (below  $V_{SS}$ ).



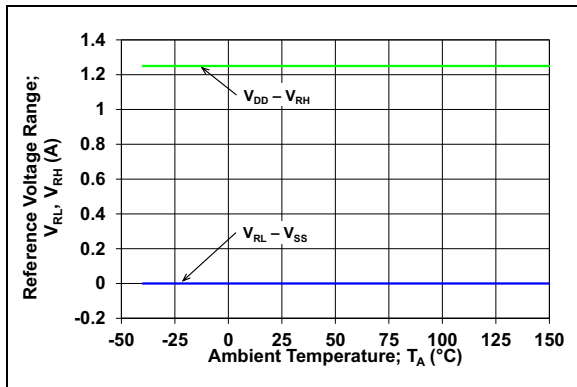
**FIGURE 2-45:** Output Voltage Range vs. Output Current.



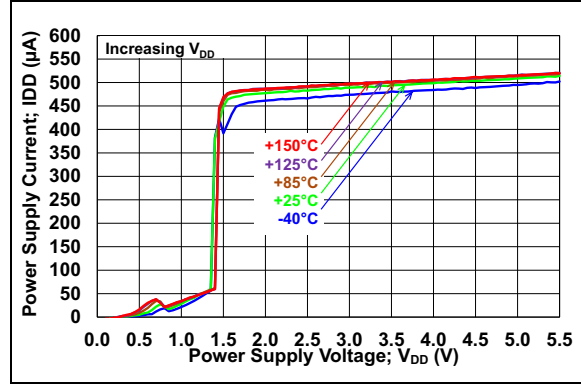
**FIGURE 2-43:** Common-Mode Input Range vs. Ambient Temperature.



**FIGURE 2-46:** Output Voltage Range vs. Ambient Temperature.



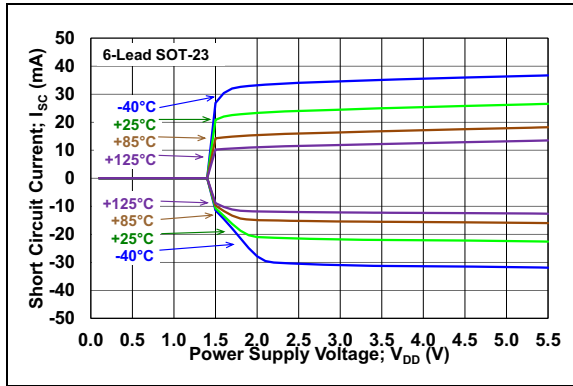
**FIGURE 2-44:** Reference Voltage Range vs. Ambient Temperature.



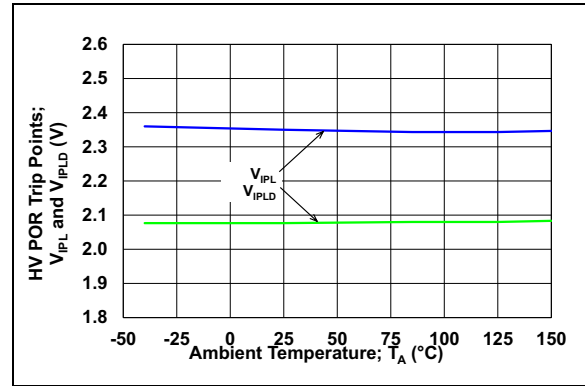
**FIGURE 2-47:** Supply Current vs. Power Supply Voltage.



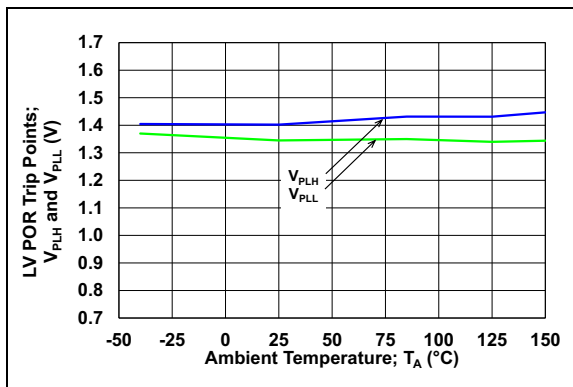
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).



**FIGURE 2-48:** Output Short Circuit Current vs. Power Supply Voltage.



**FIGURE 2-50:** HV POR (for  $V_{IP}$ ) Trip Points vs. Ambient Temperature.

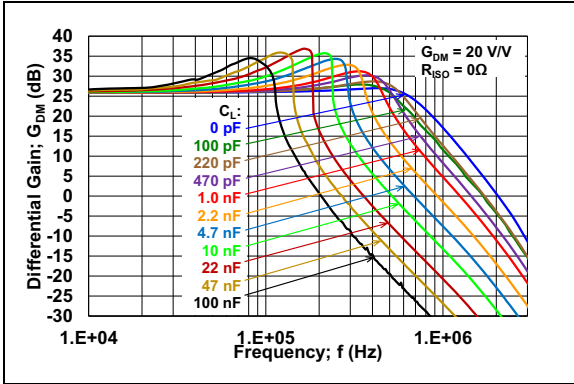


**FIGURE 2-49:** LV POR (for  $V_{DD}$ ) Trip Points vs. Ambient Temperature.

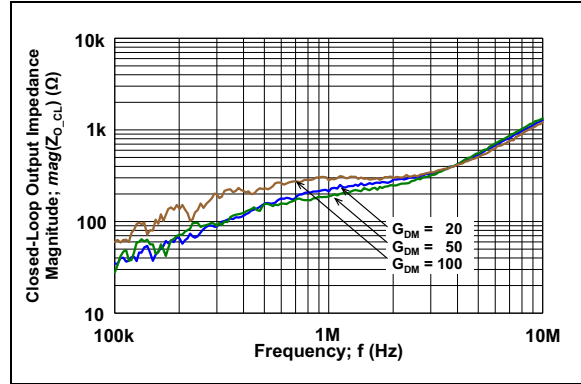
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**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).

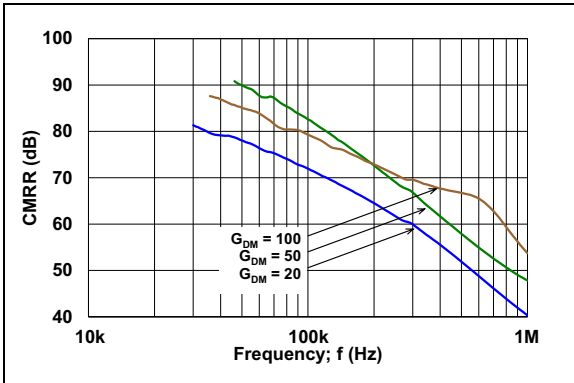
## 2.3 Frequency Response



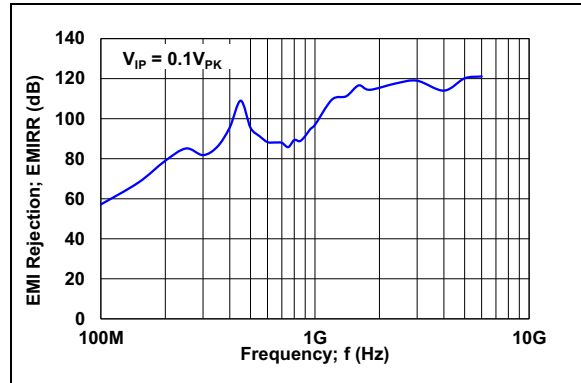
**FIGURE 2-51:** Gain vs. Frequency, with Capacitive Load.



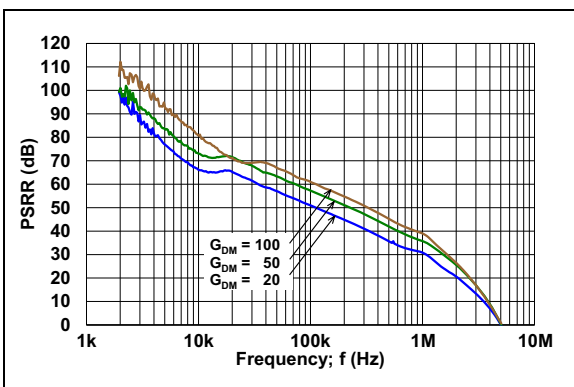
**FIGURE 2-54:** Closed-Loop Output Impedance Magnitude vs. Frequency.



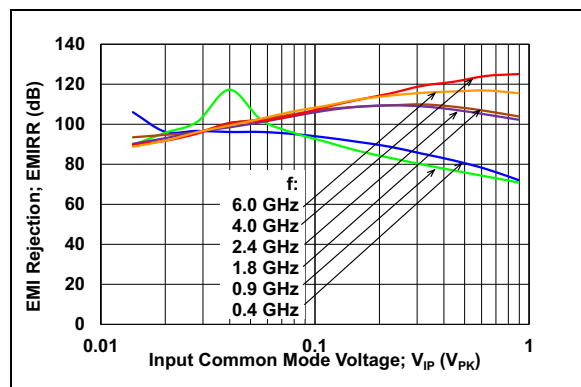
**FIGURE 2-52:** CMRR vs. Frequency.



**FIGURE 2-55:** EMI Rejection Ratio vs. Frequency.



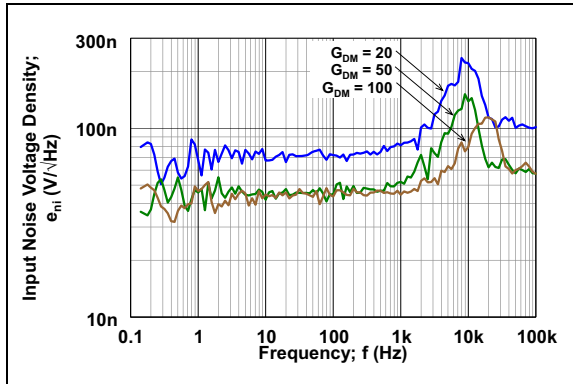
**FIGURE 2-53:** PSRR vs. Frequency.



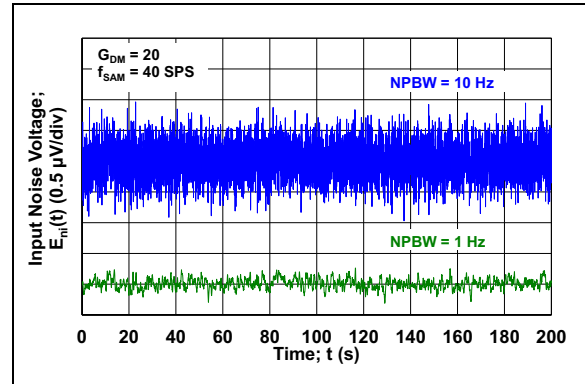
**FIGURE 2-56:** EMI Rejection Ratio vs. Signal Strength.

**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to }5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).

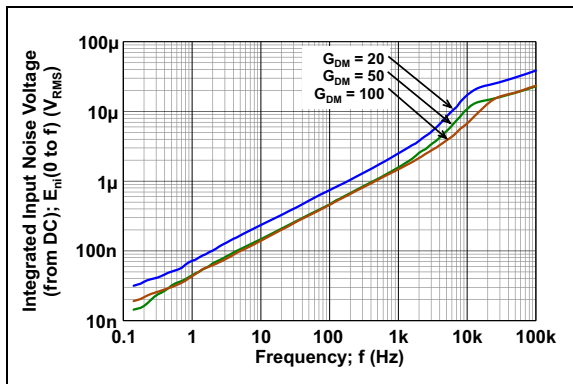
## 2.4 Noise and Intermodulation Distortion



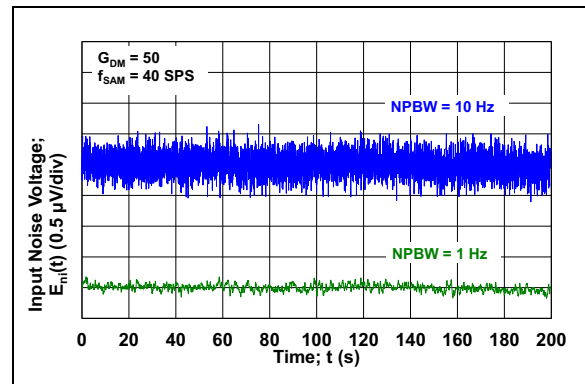
**FIGURE 2-57:** Input Noise Voltage Density vs. Frequency.



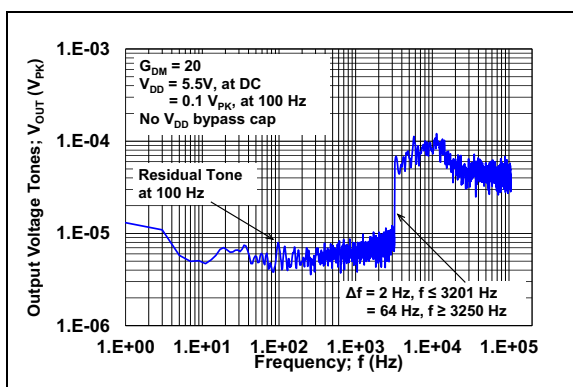
**FIGURE 2-60:** Input Noise Voltage vs. Time,  $G_{DM} = 20$ .



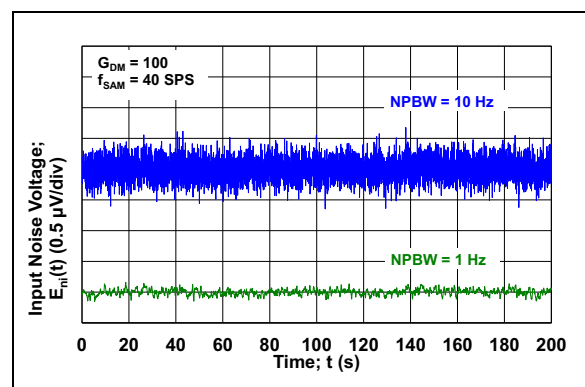
**FIGURE 2-58:** Input Noise Voltage vs. Frequency.



**FIGURE 2-61:** Input Noise Voltage vs. Time,  $G_{DM} = 50$ .



**FIGURE 2-59:** Intermodulation Distortion vs. Frequency, with  $V_{DD}$  Disturbance.

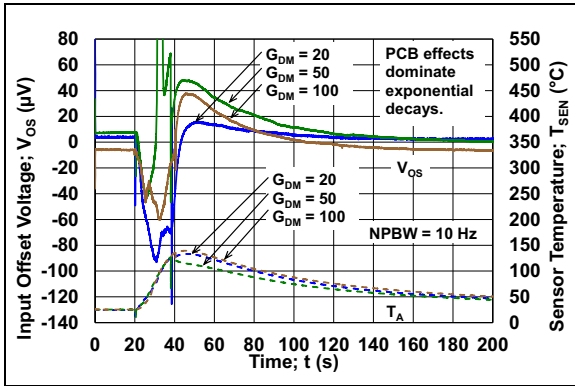


**FIGURE 2-62:** Input Noise Voltage vs. Time,  $G_{DM} = 100$ .

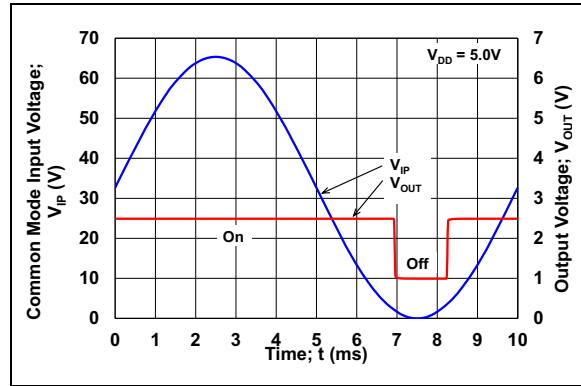
# MCP6C02

**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).

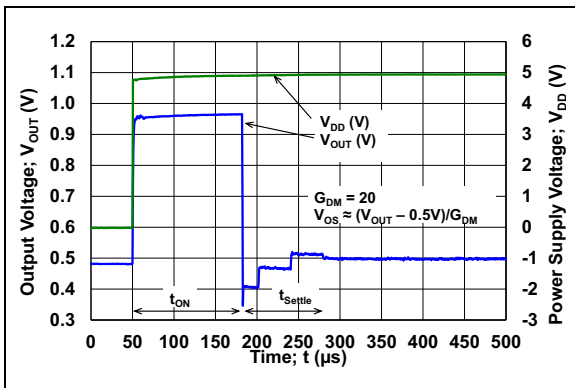
## 2.5 Time Response



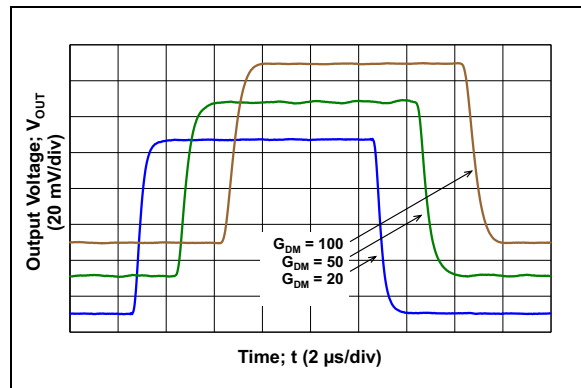
**FIGURE 2-63:** Input Offset Voltage vs. Time, with Temperature Change.



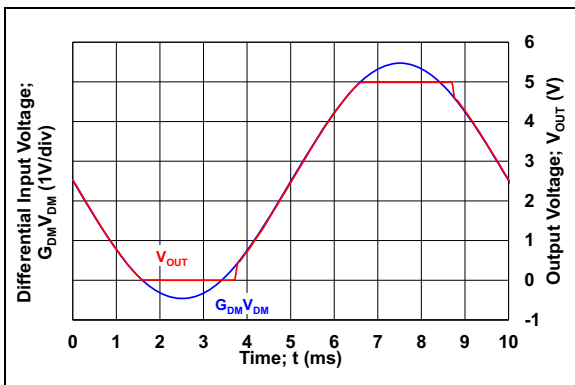
**FIGURE 2-66:** The MCP6C02 Shows No Phase Reversal vs. Input Common-Mode Overdrive.



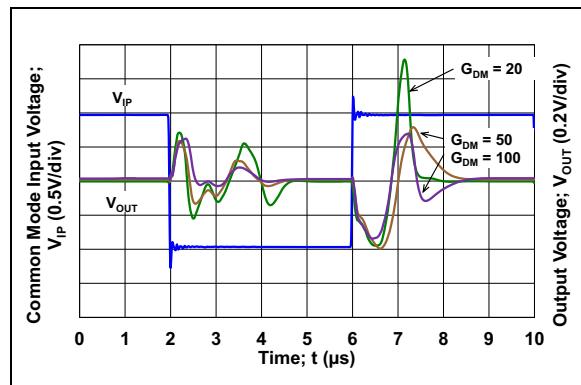
**FIGURE 2-64:** Input Offset Voltage vs. Time, at Power-Up.



**FIGURE 2-67:** Small Signal Step Response to Differential Input Voltage.

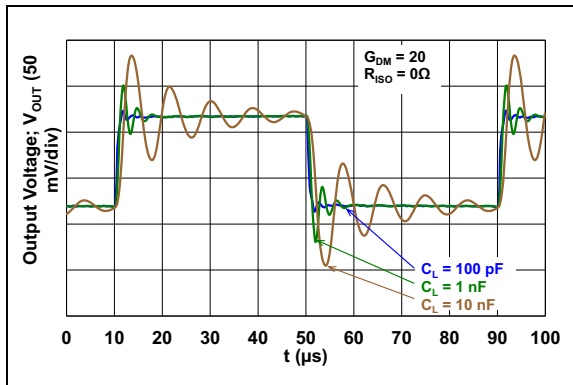


**FIGURE 2-65:** The MCP6C02 Shows No Phase Reversal vs. Differential Input Overdrive.

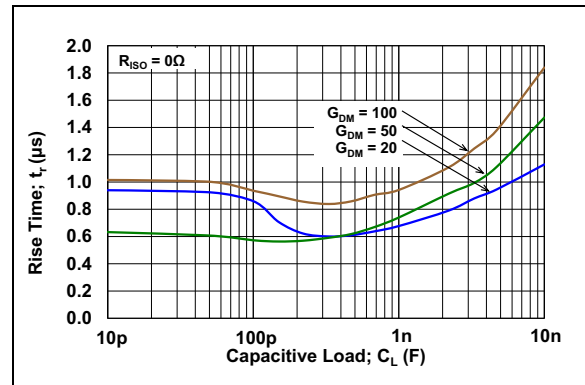


**FIGURE 2-68:** Small Signal Step Response to Common-Mode Input Voltage.

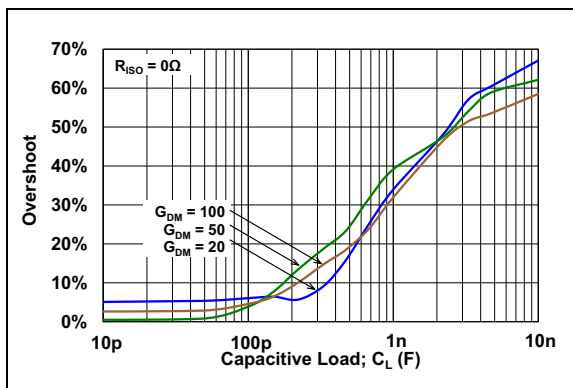
**Note:** Unless otherwise indicated,  $T_A = +25^\circ\text{C}$ ,  $V_{DD} = 2.0\text{V to } 5.5\text{V}$ ,  $V_{SS} = \text{GND}$ ,  $V_{IP} = 34\text{V}$ ,  $V_{DM} = 0\text{V}$ ,  $V_{REF} = V_{DD}/4$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10\text{ k}\Omega$  to  $V_L$  and  $C_L = 60\text{ pF}$ ; see [Figure 1-9](#), [Figure 1-10](#) and [Figure 1-11](#).



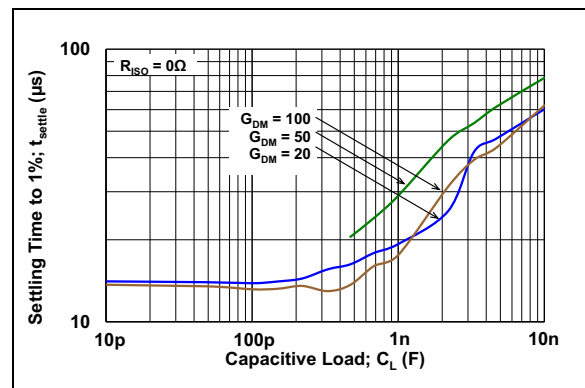
**FIGURE 2-69:** Small Signal Step Response to Differential Input Voltage, with Capacitive Load ( $C_L$ ).



**FIGURE 2-71:** Small Signal Step Response Rise Time, with Capacitive Load ( $C_L$ ).



**FIGURE 2-70:** Small Signal Step Response Overshoot, with Capacitive Load ( $C_L$ ).



**FIGURE 2-72:** Small Signal Step Response Settling Time, with Capacitive Load ( $C_L$ ).

# MCP6C02

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NOTES:

### 3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in [Table 3-1](#).

**TABLE 3-1: PIN FUNCTION TABLE**

MCP6C02 SOT-23	Symbol	Description
1	$V_{OUT}$	Output voltage
2	$V_{SS}$	Negative power supply
3	$V_{IP}$	Noninverting input (at load's $R_{SH}$ ) and positive (high-side) power supply
4	$V_{IM}$	Inverting input (at load's $R_{SH}$ )
5	$V_{REF}$	Output reference
6	$V_{DD}$	Positive (low-side) power supply

#### 3.1 Noninverting Analog Signal Input ( $V_{IP}$ )

The noninverting input ( $V_{IP}$ ) is a high-impedance CMOS input. It is designed to operate over a wide voltage range, with a voltage source to drive it. In this data sheet, it is treated as the Common-mode input voltage.

$V_{IP}$  is the high voltage power supply pin, and is normally between  $V_{SS} + 3V$  and  $V_{SS} + 65V$ . It supplies the current needed to operate the high voltage circuitry.  $V_{IP}$  should have a good bypass capacitor (e.g., 10 nF).  $V_{IP} - V_{SS}$  triggers the HV POR.

#### 3.2 Inverting Analog Signal Input ( $V_{IM}$ )

The inverting input ( $V_{IM}$ ) is a high-impedance CMOS input, with low input bias current.  $V_{IM}$  is designed to operate near the  $V_{IP}$  voltage. The difference voltage  $V_{DM}$  (or  $V_{IP} - V_{IM}$ ) is the input signal for this amplifier.

#### 3.3 Analog Output Reference Voltage ( $V_{REF}$ )

The analog output reference voltage is a high-impedance CMOS input.  $V_{REF}$  is set to a DC voltage, which shifts  $V_{OUT}$ . Its dynamic response helps reject power surges and glitches at the  $V_{IP}$ ,  $V_{DD}$  and  $V_{SS}$  pins.

#### 3.4 Analog Output ( $V_{OUT}$ )

The analog output pin ( $V_{OUT}$ ) is a low-impedance voltage source.

#### 3.5 Low-Side Power Supplies ( $V_{DD}$ , $V_{SS}$ )

$V_{DD}$  is normally between  $V_{SS} + 2.0V$  and  $V_{SS} + 5.5V$ , while the  $V_{REF}$  and  $V_{OUT}$  pins are usually between  $V_{SS}$  and  $V_{DD}$ .  $V_{DD} - V_{SS}$  triggers the LV POR.

Typically, these parts are used in a single (positive) supply configuration. In this case,  $V_{SS}$  is connected to ground and  $V_{DD}$  is connected to the supply.  $V_{DD}$  will need good bypass capacitors.

In split supply configurations, including dual supplies, ground is between  $V_{SS}$  and  $V_{DD}$ . Both supply pins will need good bypass capacitors.

In a single (negative) supply configuration,  $V_{DD}$  connects to ground and  $V_{SS}$  connects to the supply.  $V_{SS}$  will need good bypass capacitors.

# MCP6C02

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NOTES:



## 4.0 DEVICE OPERATION

This chapter includes additional information on basic operations and major functions.

### 4.1 Basic Performance

#### 4.1.1 IDEAL PERFORMANCE

Figure 4-1 shows the basic circuit; inputs, supplies and output. When the inputs ( $V_{IP}$ ,  $V_{IM}$ ,  $V_{DD}$ ,  $V_{SS}$  and  $V_{REF}$ ) and output ( $V_{OUT}$ ) are in their specified ranges, and the part is nearly ideal, the output voltage is:

#### EQUATION 4-1:

$$V_{OUT} \approx V_{REF} + G_{DM}V_{DM}$$

Where:

- $G_{DM}$  = Differential-Mode Gain
- $V_{IP}$  = Common-Mode Input (and HV supply)
- $V_{DM}$  = Differential-Mode Input ( $V_{IP} - V_{IM}$ )

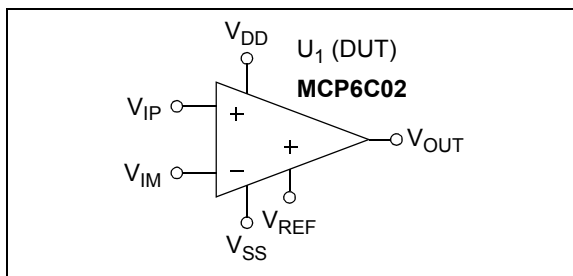


FIGURE 4-1: Basic Circuit.

For normal operation, keep:

- $V_{IP}$  between  $V_{IPL}$  and  $V_{IPH}$
- $V_{DM}$  between  $V_{DML}$  and  $V_{MDH}$
- $V_{REF}$  between  $V_{RL}$  and  $V_{RH}$
- $V_{OUT}$  between 0.1V to  $V_{DD} - 0.1V$ , usually
  - $V_{OL}$  and  $V_{OH}$  are hard limits

#### 4.1.2 ANALOG ARCHITECTURE

Figure 4-2 shows the block diagram for these high-side current sense amplifiers, without any details on offset correction.

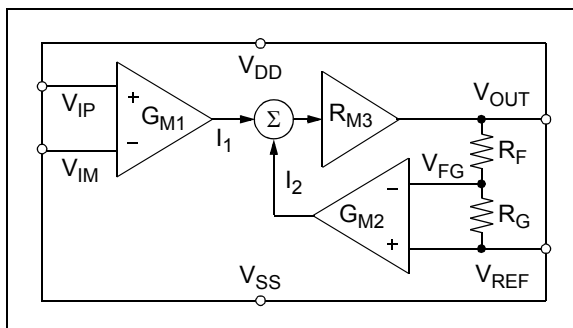


FIGURE 4-2: MCP6C02 Block Diagram.

The input (differential) signal is applied to  $G_{M1}$ . Due to its architecture, the MCP6C02's signal inputs are best described by  $V_{IP}$  and  $V_{DM}$ . The inverting input is then:

#### EQUATION 4-2:

$$V_{IM} = V_{IP} - V_{DM}$$

The negative feedback loop includes  $G_{M2}$ ,  $R_{M3}$ ,  $R_F$  and  $R_G$ . These blocks set the DC open-loop gain ( $A_{OL}$ ) and the nominal differential gain ( $G_{DM}$ ):

#### EQUATION 4-3:

$$A_{OL} = G_{M2}R_{M3}$$

$$G_{DM} = 1 + R_F/R_G$$

$A_{OL}$  is very high, so the current into  $R_{M3}$  ( $I_1 + I_2$ ) is nearly zero. This makes the differential inputs to  $G_{M1}$  and  $G_{M2}$  equal in magnitude and opposite in polarity. Ideally, this gives:

#### EQUATION 4-4:

$$V_{FG} - V_{REF} = V_{DM}$$

$$V_{OUT} = V_{REF} + G_{DM}V_{DM}$$

For an ideal part, within the operating ranges, changing  $V_{IP}$ ,  $V_{SS}$  or  $V_{DD}$  produces no change in  $V_{OUT}$ .  $V_{REF}$  shifts  $V_{OUT}$  as needed in the design.

The different  $G_{DM}$  options change  $G_{M1}$ ,  $G_{M2}$ ,  $R_F$ ,  $R_G$  and the internal compensation capacitor. This results in the performance trade-offs highlighted in Table 1.

### 4.1.3 DC PERFORMANCE

#### 4.1.3.1 DC Voltage Errors

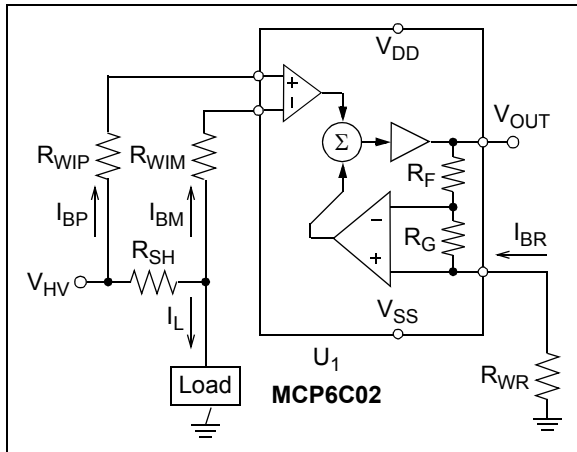
Section 1.6, Explanation of DC Error Specifications covers some DC specifications. The input offset error (with temperature coefficients), gain error and nonlinearities are discussed in detail.

Plots in Section 2.1, DC Precision and Section 2.2, Other DC Voltages and Currents give useful information.

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## 4.1.3.2 DC Current Errors

Figure 4-3 shows the resistors and currents that change the DC bias point. The input bias currents ( $I_{BP}$ ,  $I_{BM}$  and  $I_{BR}$ ), together with a circuit's external input resistances, give an DC error (see Equation 1-2).



**FIGURE 4-3:** DC Bias Resistors and Currents.

$R_{SH}$  is set by the design requirements, given the load current ( $I_L$ ). For most applications,  $R_{SH}$  would be between 100  $\mu\Omega$  and 1 $\Omega$ .

The DC input offset error due to the input currents is:

$$\begin{aligned} V_{OS\_IR} &= V_{DM} - I_L R_{SH} \\ &= I_{BM}(R_{SH} + R_{WIM}) - I_{BP}R_{WIP} \end{aligned}$$

Since these currents do not correlate, minimize the magnitude of each resistance.  $I_{BP}R_{IP}$  will dominate in many designs.

### EQUATION 4-6:

$$P_{LV} = (V_{IP} - V_{SS})I_{BP} + (V_{DD} - V_{SS})I_{DD} + (V_{DD} - V_{OUT})\max(0A, I_{OUT}) + (V_{OUT} - V_{SS})\max(0A, -I_{OUT})$$

Now we can estimate the junction temperature of the device (see Table 1-4):

### EQUATION 4-7:

$$T_J = T_A + P_{LV}\theta_{JA}$$

## 4.1.6 AC PERFORMANCE

The AC response is designed to be stable. This is seen in the frequency response's low gain peaking and the step response's low overshoot. This stability assumes  $V_{REF}$  sees a low impedance and the capacitive load at  $V_{OUT}$  is low.

The small signal bandwidth is set internally; stable designs will show bandwidths similar to the specification. The large signal bandwidth is close to the small signal bandwidth; slew rate (SR) has little effect on  $V_{OUT}$  (a benefit of our current-mode architecture).

$R_{WR}$  modifies the gain error and the DC output offset error ( $V_{OUT}$  changes  $I_{BR}$ ):

### EQUATION 4-5:

$$\begin{aligned} \Delta V_{REF} &= -I_{BR}R_{WR} \\ \Delta g_E &\approx (-R_{WR}G_{DM})/(R_F + R_G) \\ V_{OUT} &\approx (V_{REF} + \Delta V_{REF}) + G_{DM}V_{DM}(I + g_E + \Delta g_E) \end{aligned}$$

## 4.1.4 AC PERFORMANCE

The bandwidth of these parts ( $f_{BW}$ ) is set internally to either 500 kHz ( $G_{DM} = 20$  or 50) or 390 kHz ( $G_{DM} = 100$ ).

The bandwidth at the maximum output swing is called the Full Power Bandwidth ( $f_{FPBW}$ ). It is limited by the Slew Rate (SR) for many amplifiers, but is close to  $f_{BW}$  for these parts. This is a benefit of the current-mode architecture these parts have.

These parts are compensated to have a stable response. For instance, step response overshoot is low.

## 4.1.5 TEMPERATURE PERFORMANCE

The input offset voltage's temperature drift is detailed in Equation 1-6. Other temperature responses are shown in Section 1.3, Specifications and Section 2.0 "Typical Performance Curves".

Since there are three power supply pins ( $V_{IP}$ ,  $V_{DD}$  and  $V_{SS}$ ), and  $V_{IP}$  reaches 65V, power and temperature rise calculations are important.

The power dissipated is calculated as follows ( $I_{OUT}$  is positive when it flows out of the  $V_{OUT}$  pin):

## 4.1.7 NOISE PERFORMANCE

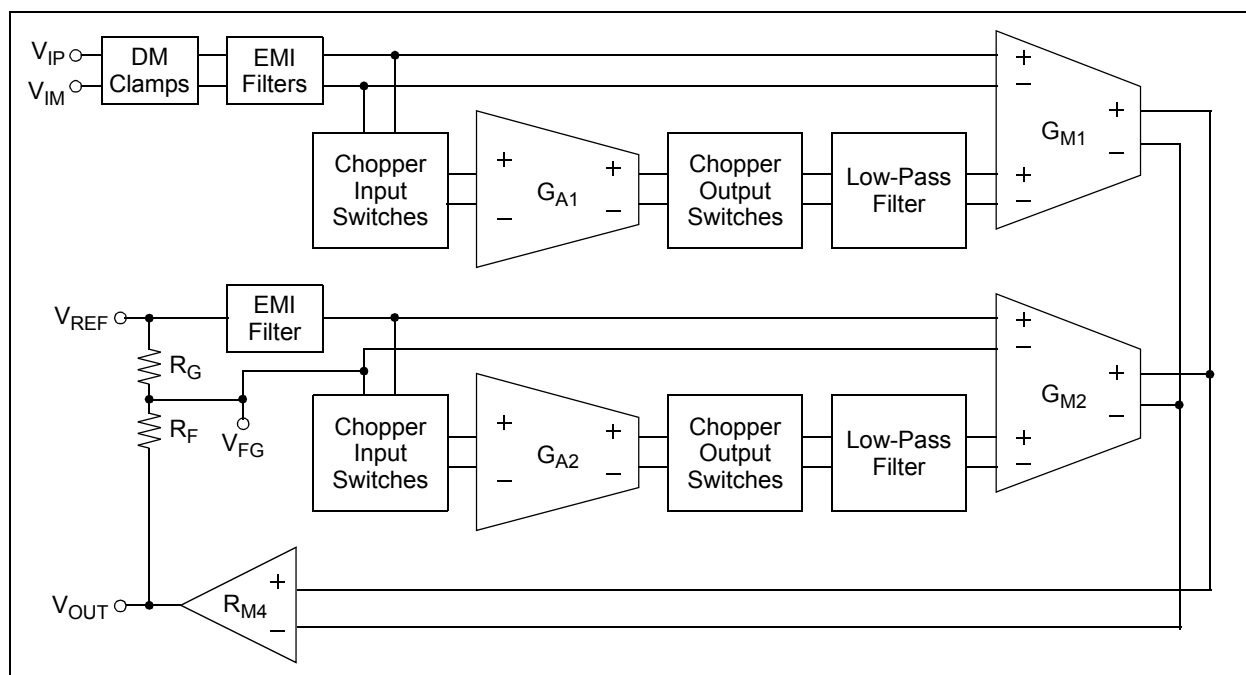
This part is designed to have low input noise voltage density at lower frequencies. The offset correction (Section 4.2.2, Chopping Action) modulates high frequency white noise down to DC; it also modulates low frequency 1/f noise to higher frequencies.

The measured input noise voltage density is shown in Figure 2-57. That figure also shows Integrated Input Noise Voltage ( $E_{ni}$ , in units of  $V_{RMS}$ ) between 0 Hz and  $f$  (between 0.1 Hz and 100 kHz).

The Input Noise Voltage Density ( $e_{ni}$ ) changes with  $V_{DM}$ . However, that relationship is a weak one.

## 4.2 Overview of Zero-Drift Operation

Figure 4-4 shows a diagram of the MCP6C02; It explains how slow voltage errors at the input are reduced in this architecture (much better  $V_{OS}$ ,  $TC_1$ ,  $TC_2$ , CMRR, CMRR2, PSRR and  $1/f$  noise).



**FIGURE 4-4:** MCP6C02 Block Diagram.

### 4.2.1 BUILDING BLOCKS

The Main Amplifiers ( $G_{M1}$  and  $G_{M2}$ ) are designed for high gain and bandwidth, with a differential topology. The main input pairs (+ and - pins at the top left) are for the higher frequency portion of the input signal. The auxiliary input pairs (+ and - pins at the bottom left) are for the low frequency and high precision portion of the input signal and correct the input offset voltage. Both inputs are added together internally.

The Auxiliary Amplifiers ( $G_{A1}$  and  $G_{A2}$ ), the Chopper Input Switches and the Chopper Output Switches provide a high DC gain to the input signal. DC errors are modulated to higher frequencies and white noise to low frequencies.

The Low-Pass Filter reduces high-frequency content, including harmonics of the Chopping Clock.

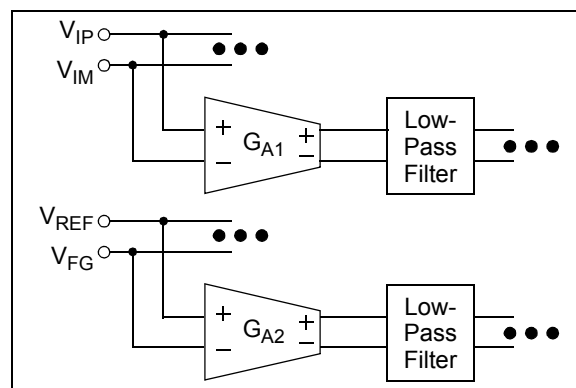
The Output Buffer ( $R_{M4}$ ) converts current to voltage, drives the external load at  $V_{OUT}$  and creates a negative feedback loop through  $R_F$  and  $R_G$ .  $R_F$  and  $R_G$  help set the differential gain.

The Oscillator runs at  $f_{CLK} = 50$  kHz for the gains of 20 and 50, and at  $f_{CLK} = 100$  kHz for the gain of 100.  $f_{CLK}$  is divided by 2, to produce the Chopping Clock rate (25 kHz and 50 kHz, respectively).

The internal LV POR (for  $V_{DD} - V_{SS}$ ) starts the part in a known good state, protecting against power supply brown-outs. The internal HV POR (for  $V_{IP} - V_{SS}$ ) ensures protection of the low voltage circuitry, as well as proper functioning.

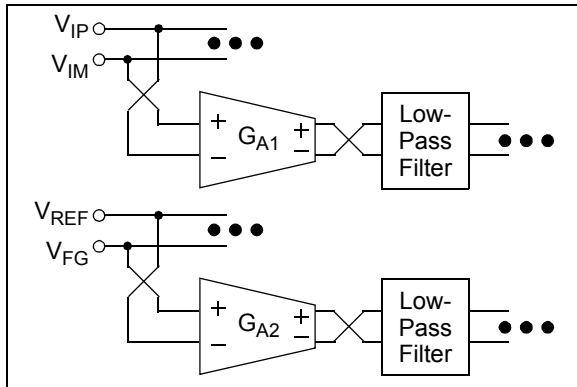
### 4.2.2 CHOPPING ACTION

Figure 4-5 shows the amplifier connections for the first phase of the Chopping Clock and Figure 4-6 shows them for the second phase. The slow voltage errors alternate in polarity, making the average error small.



**FIGURE 4-5:** First Chopping Clock Phase; Simplified Diagram.

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**FIGURE 4-6:** Second Chopping Clock Phase; Simplified Diagram.

## 4.2.3 FINAL TEST VS. BENCH

Due to limitations in the final test environment (e.g., equipment accuracies, thermocouple effects crosstalk and test time), final test measurements are not as accurate as bench measurements. For this reason, the input offset voltage related specifications ( $V_{OS}$ ,  $TC_1$ ,  $TC_2$ , ...,  $CMRR$  and  $PSRR$ ) are significantly wider than the histograms from bench measurements.

The bench results will give good guidance on how to design your circuit. The specified limits (for final test) give min/max limits used to screen outliers in production.

## 4.2.4 INTERMODULATION DISTORTION (IMD)

These amplifiers will show intermodulation distortion (IMD) products when an AC signal is present.

The signal and clock can be decomposed into sine wave tones (Fourier series components). These tones interact with the zero-drift circuitry's nonlinear response to produce IMD tones at sum and difference frequencies. Each of the square wave clock's harmonics has a series of IMD tones centered on it.

## 4.3 Protection

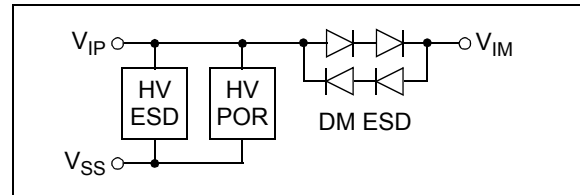
The MCP6C02 helps the designer provide enough protection against undesired conditions and signals in their environment.

### 4.3.1 INTERNAL PROTECTION DEVICES

All of the ESD structures clamp their inputs when they try to go too far below  $V_{SS}$ . Their breakdown voltage is high enough to allow normal operation, but not low enough to protect against slow over-voltage events. Very fast ESD events (that meet the specification) are limited so that damage does not occur.

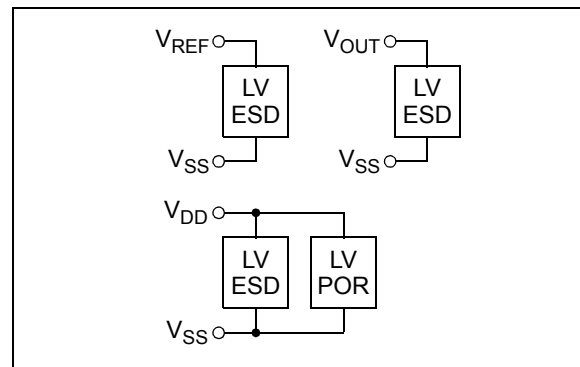
The supply inputs ( $V_{IP} - V_{SS}$  and  $V_{DD} - V_{SS}$ ) are also connected to PORs, so that internal power up sequencing is well controlled.

The  $V_{IP}$  and  $V_{IM}$  input pins have an ESD structure designed to limit  $V_{IP} - V_{SS}$  and  $V_{DM}$ . The double parallel diode structure that limits ESD damage through  $V_{DM}$  also limits  $V_{DM}$  in other conditions.



**FIGURE 4-7:** Input Protection for  $V_{DM}$  (i.e., for  $V_{IM}$  and  $V_{IP} - V_{SS}$ ).

The  $V_{REF}$ ,  $V_{OUT}$  and  $V_{DD}$  pins have ESD structures that limit their voltages above  $V_{SS}$  (i.e., limit  $V_{REF} - V_{SS}$ ,  $V_{OUT} - V_{SS}$  and  $V_{DD} - V_{SS}$ ).



**FIGURE 4-8:** Input Protection for  $V_{REF}$ ,  $V_{OUT}$  and  $V_{DD}$ .

### 4.3.2 PHASE REVERSAL

This part is designed to not exhibit phase inversion when the input signals ( $V_{IP}$ ,  $V_{DM}$  and  $V_{REF}$ ) exceed their specified ranges (but not their absolute ranges).

## 5.0 APPLICATIONS

This chapter includes design recommendations and typical application circuits.

The Common-mode rejection (see [Figure 2-16](#), [Figure 2-17](#), [Figure 2-18](#) and [Figure 2-52](#)) supports applications in noisy environments. Our Current-mode architecture gives high CMRR at higher frequencies than was traditional (e.g., 80 dB near 80 kHz, instead of near 60 Hz).

The power supply rejection (see [Figure 2-53](#)) also has excellent rejection at higher frequencies than traditional.

### 5.1 Recommended Design Practices

Some simple design practices help take advantage of the MCP6C02's performance in high side current sensing applications.

#### 5.1.1 INPUT VOLTAGE LIMITS

To prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages at the  $V_{IP}$  and  $V_{IM}$  input pins, as well as the differential input voltage  $V_{DM}$  (see [Section 1.1, Absolute Maximum Ratings †](#)). These requirements are independent of the current limits discussed below.

The ESD protection on the  $V_{IP}$  and  $V_{DM}$  inputs was discussed in [Section 4.3.1, Internal Protection Devices](#). This structure was chosen to protect the input transistors against many (but not all) overvoltage conditions, and to minimize input bias currents ( $I_{BP}$  and  $I_{BM}$ ).

To protect the inputs, always drive  $V_{IP}$  with a low impedance source and use a shunt resistor ( $R_{SH}$ ) with low resistance (designed to not fail open). Placing zener diode(s) or a transistor across  $R_{SH}$  will also help protect the inputs.

#### 5.1.2 INPUT CURRENT LIMITS

To prevent damage to (or improper operation of) these amplifiers, the circuit must limit the currents into the  $V_{IP}$  and  $V_{IM}$  input pins (see [Section 1.1, Absolute Maximum Ratings †](#)). This requirement is independent of the voltage limits discussed above.

One way to ensure the input currents are limited is to always drive  $V_{IP}$  with a low impedance source, and to use a shunt resistor ( $R_{SH}$ ) with low resistance (designed to not fail open). Placing zener diode(s) or a transistor across  $R_{SH}$  will also help protect the inputs.

#### 5.1.3 BYPASS CAPACITORS

Be sure to specify capacitors that will support your application. Be sure to look at:

- Voltage Rating (well above the maximum value for its pins)
- Dielectrics (good Temp. Cos. and reasonable Volt. Cos.)
- Size
- Surface Mount vs. Leaded
- Cost vs. availability

If possible, connect  $V_{SS}$  to ground. This will make your design simpler.

Bypass  $V_{IP}$  to  $V_{SS}$  with a local bypass capacitor next to these pins (e.g., 10 nF). If needed, a bulk bypass capacitor can also be added (e.g., 1  $\mu$ F).

Bypass  $V_{DD}$  to  $V_{SS}$  with a local bypass capacitor next to these pins (e.g., 100 nF). A bulk bypass capacitor should also be added close by (e.g., 2.2  $\mu$ F); placing it next to the local bypass capacitor is a good choice.

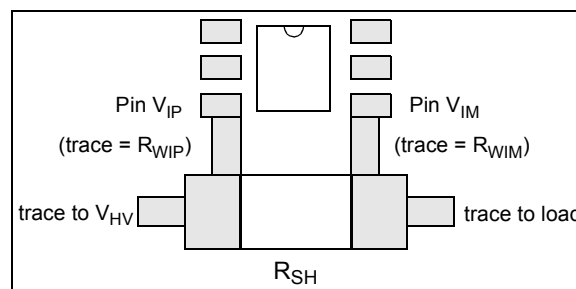
#### 5.1.4 SETTING THE VOLTAGES AT $V_{IP}$ AND $V_{IM}$

$V_{IP}$  is tied to a voltage source, to minimize glitches and crosstalk. This part's excellent CMRR versus frequency helps reject Common-mode (i.e., at  $V_{IP}$ ) noise and glitches. A local pass capacitor to  $V_{SS}$  can help, when the design allows it; 10 nF is usually a good choice (see the [Typical Application Circuit](#) on [Page 1](#)).

A shunt resistor ( $R_{SH}$ ) is connected between  $V_{IP}$  and  $V_{IM}$ , then to the load (which is grounded). It is selected for the trade-off between accuracy (high  $R_{SH}$ ) and power dissipation (low  $R_{SH}$ ). Low power dissipation also leads to reduced size and cost.  $R_{SH}$  also helps protect these pins against large glitches; make sure it will never fail open.

Bypass capacitors on  $V_{IP}$  and  $V_{IM}$  can reduce the risk of high over-voltage events, when the current changes abruptly (such as an inductive load opening).

A good layout is necessary to minimize DC and AC errors. [Figure 5-1](#) shows a layout that minimizes input resistances seen by  $I_{BN}$  and  $I_{BM}$ . The critical paths are between  $R_{SH}$  and the pins  $V_{IP}$  and  $V_{IM}$  ( $R_{WIP}$  and  $R_{WIM}$ ).



**FIGURE 5-1:** PCB Layout for  $R_{SH}$  (connections to  $V_{IP}$  and  $V_{IM}$ ).

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For accuracy, the wiring resistances at the DUT inputs need to be small:

## EQUATION 5-1:

$$R_{WIP} \leq 4 \text{ m}\Omega$$

$$R_{WIM} \leq 0.1\Omega$$

### 5.1.5 SETTING THE VOLTAGE AT $V_{REF}$

For designs with  $V_{REF} = V_{SS}$ , short the  $V_{REF}$  and  $V_{SS}$  pins together; connect them to ground (or other reference) using one low impedance via (or trace). This minimizes DC and AC errors.

For designs with  $V_{REF} \geq V_{SS} + 0.1V$ , connect  $V_{REF}$  and  $V_{SS}$  with a relatively large capacitor. Since  $V_{REF}$  needs a low impedance source, we recommend the following two design approaches.

The DC resistance seen at  $V_{REF}$  needs to be small. This resistance includes trace resistance, via resistance and output resistance of any driving amplifiers. For good gain error in the signal band, maintain this resistance in that band.

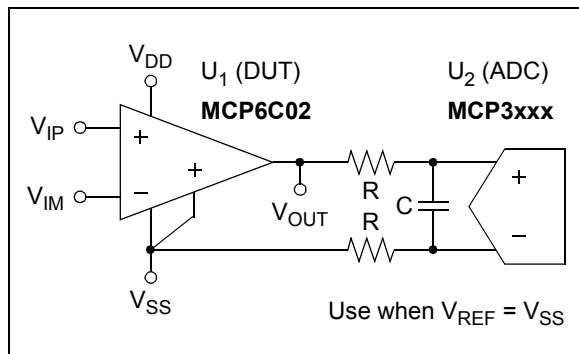
## EQUATION 5-2:

$$R_{WR} \leq 1\Omega$$

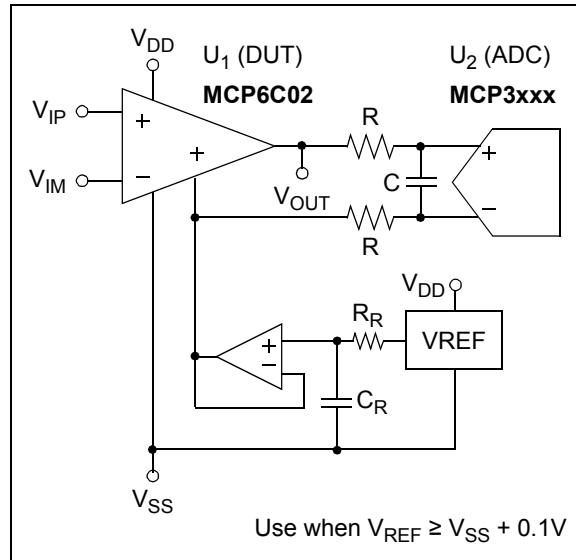
The AC impedance seen at  $V_{REF}$  needs to support stability at frequencies near the bandwidth. See [Section 5.1.7.1, Driving VREF](#) for more information.

[Figure 5-2](#) shorts  $V_{REF}$  and  $V_{SS}$  together. The ADC connects its negative input to  $V_{REF}$ , so it can reject glitches on  $V_{SS}$  and  $V_{REF}$  (notice only one connection to  $V_{SS}$  is shown, for good precision).

[Figure 5-3](#) uses an IC VREF to generate  $V_{REF} - V_{SS}$ , an R-C low-pass filter to reject fast glitches seen at  $V_{REF} - V_{SS}$  and an op amp buffer ( $\geq 1 \text{ MHz}$ ) to drive  $V_{REF}$  with a low impedance source (see [Equation 1-2](#)) (notice only one connection to  $V_{SS}$  is shown, for good precision).



**FIGURE 5-2:**  $V_{REF}$  Bypass Circuit #1.



**FIGURE 5-3:**  $V_{REF}$  Bypass Circuit #2.

Replacing [Figure 5-3](#) with a simple resistor divider and capacitor will cause potential issues. The equivalent resistance needs to be low (see [Equation 5-2](#)), so the divider will draw a lot of current. The capacitor will need to be large, to set a reasonable pole, increasing cost and PCB space.

We strongly recommend against designs with  $V_{SS} < V_{REF} < V_{SS} + 0.1V$ , since AC glitches may become a problem.

### 5.1.6 TEMPERATURE RISE

Make sure that  $T_J$  does not exceed the Absolute Maximum Junction Temperature spec (see [Section 1.1, Absolute Maximum Ratings](#)). This is a strong concern when  $T_A$  is high (e.g., above  $125^\circ\text{C}$ ), when  $I_{OUT}$ 's magnitude is large (e.g., near the short circuit limit) or when  $V_{IP}$  is high.

Formulas needed for this part of the design are found in [Section 4.1.5, Temperature Performance](#).

[Figure 2-63](#) shows that temperature ramp rates need to be limited, for best performance. The decay rates shown there are limited by the PCB and other components.

### 5.1.7 ENSURING STABILITY

A few simple design techniques will help take advantage of these stable parts. Simulations and bench measurements help to verify the solutions (e.g., look at step response overshoot and ringing).

## 5.1.7.1 Driving $V_{REF}$

The voltage source driving the  $V_{REF}$  pin must be low impedance (see Equation 1-2), so that the signal gain is constant within the signal bandwidth.

When the frequency is near the bandwidth (e.g., between  $BW/4$  and  $4 BW$ ), the source's impedance magnitude should be below  $50\Omega$ .

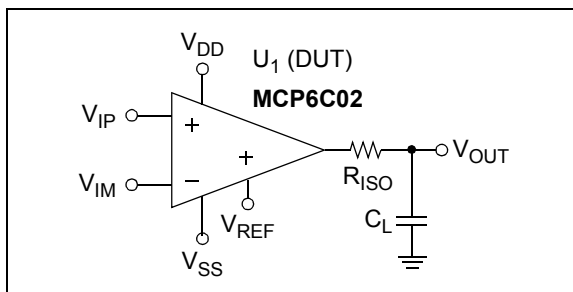
## 5.1.7.2 Source Impedances

The recommended DC source resistances (at  $V_{IP}$ ,  $V_{IM}$  and  $V_{REF}$ ; see Equation 5-2) will help ensure stability, by keeping R-C time constants very fast.

## 5.1.7.3 Capacitive Loads

Driving large capacitive loads can cause stability problems for voltage amplifiers. As the load capacitance increases, the feedback loop's phase margin decreases and the closed-loop bandwidth reduces. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. Lower gains ( $G_{DM}$ ) exhibit greater sensitivity to capacitive loads.

When driving large capacitive loads with these parts (e.g.,  $> 80$  pF), a small series resistor at the output ( $R_{ISO}$  in Figure 5-4) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitive load.

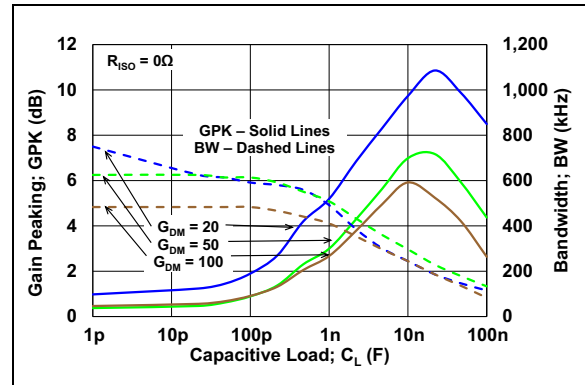


**FIGURE 5-4:** Recommended  $R_{ISO}$  Values for Capacitive Loads.

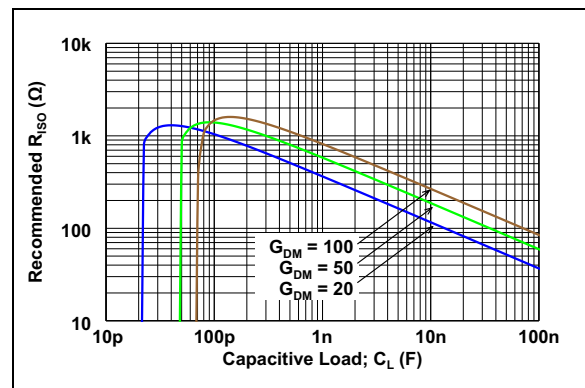
Figure 5-5 shows the typical responses versus  $C_L$ , when  $R_{ISO}$  is a short circuit (also see Figure 2-69 to Figure 2-72).

Figure 5-6 gives recommended  $R_{ISO}$  values for different capacitive loads and gains. The x-axis is the load capacitance ( $C_L$ ).

After selecting  $R_{ISO}$  for the circuit, double check the resulting frequency response peaking and step response overshoot on the bench. Modify  $R_{ISO}$ 's value until the response is reasonable.



**FIGURE 5-5:** Bandwidth and Gain Peaking vs. Capacitive Load, without  $R_{ISO}$ .



**FIGURE 5-6:** Recommended  $R_{ISO}$  vs. Capacitive Load.

## 5.1.8 NOISE DESIGN

As shown in Figure 2-57 and Table 1-3, the input noise voltage density is white (and low) at low frequencies. This supports accurate averages (DC estimates) in applications.

$1/f$  noise is negligible for almost all applications. As a result, the time domain data in Figure 2-60, Figure 2-61 and Figure 2-62 is well behaved.

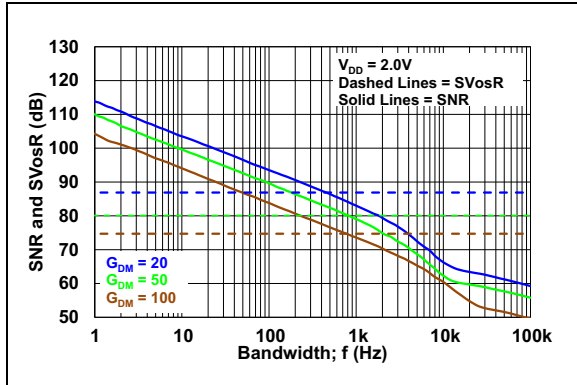
Figure 2-57 also shows a curve of the Integrated Input Noise Voltage ( $E_{ni}$ , in units of  $V_{RMS}$ ) between 0 Hz and  $f$  (between 0.1 Hz and 100 kHz). To estimate  $E_{ni}$  between the frequencies  $f_1$  and  $f_2$ , simply take the RMS difference (i.e.,  $E_{ni} |_{f_1 \text{ to } f_2} = \sqrt{E_{ni2}^2 - E_{ni1}^2}$ ).

The Input Noise Voltage Density ( $e_{ni}$ ) changes with  $V_{DM}$ ; however, that it is a weak relationship, so it can be neglected in designs.

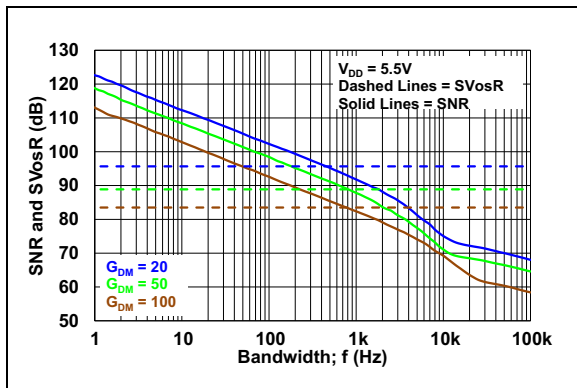
Figure 5-7 and Figure 5-8 show the device noise as a Signal-to-Noise ratio (SNR), assuming the signal is a full-scale sine wave (at  $V_{OUT}$ ). The x-axis is the circuit's bandwidth (BW), to make it easy to evaluate a particular design.

The input offset voltage is shown as a Signal-to-Offset ratio (SVoS), to indicate where the DC offset dominates the error.

# MCP6C02



**FIGURE 5-7:** SNR vs. Bandwidth Estimates,  $V_{DD} = 2.0V$ .



**FIGURE 5-8:** SNR vs. Bandwidth Estimates,  $V_{DD} = 5.5V$ .

## 5.1.9 UNIDIRECTIONAL APPLICATIONS

In unidirectional applications where  $V_{REF} = V_{SS}$ , it is important to minimize output headroom ( $V_{OL}$ ). The lower  $V_{OL}$  is, the more accurate the zero scale reading is.

To reduce  $V_{OL}$ , make  $I_{OUT}$  as low as possible. This is done by making  $R_L$  high and by tying  $V_L$  to  $V_{SS}$ .

Figure 5-2 shows how to connect  $V_{REF}$  and  $V_{SS}$  for best performance.

## 5.1.10 BIDIRECTIONAL APPLICATIONS

Figure 5-3 shows ways to connect  $V_{REF}$  and  $V_{SS}$  for best performance.

To maximize headroom, reduce  $V_{OL}$  and  $V_{OH}$  by setting  $R_L$  high.

## 5.1.11 SUPPLY PINS

As described in Section 3.5 “Low-Side Power Supplies ( $V_{DD}$ ,  $V_{SS}$ )”, the ground potential (GND) can be set where needed in your design. The most common design approach has  $V_{SS} = GND$  (positive single supply). Other common design approaches have  $V_{DD} = GND$  (negative single supply) or  $V_{SS} < GND < V_{DD}$  (dual, or split, supplies).

Setting  $V_{SS} = GND$  has the potential to increase rejection of crosstalk and glitches. In any case, a good ground design (e.g., ground plane on a PCB) and appropriate bypass capacitors are needed to realize these benefits. It pays to be sure that your capacitor's voltage rating and dielectric will support your needs over your voltage and temperature ranges. With some dielectrics, it pays to also take aging (changes over time) into account too.



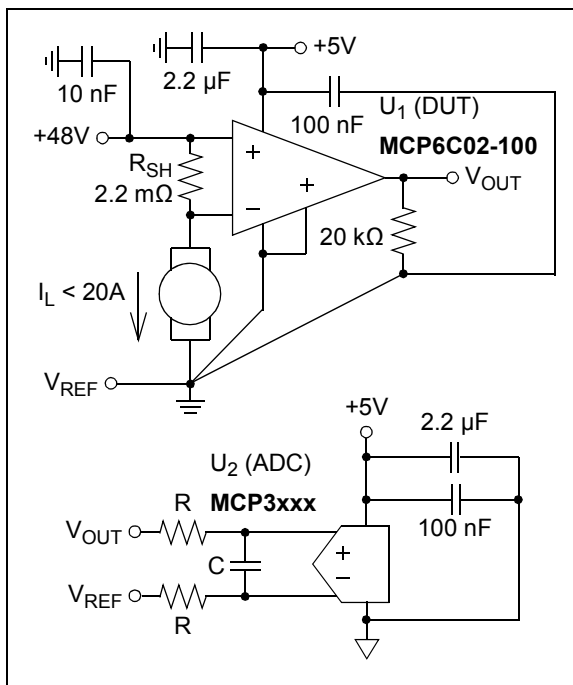
## 5.2 Typical Application Circuits

The following circuits give guidance on using the MCP6C02 within common applications. They leave out details and the design requirements followed.

### 5.2.1 MOTOR CURRENT MONITORS

Figure 5-9 shows a simplified DC Motor Current Monitor circuit with a regulated voltage supply. The MCP6C02 and its circuit are all connected to the same ground, for better glitch performance. In this case, since  $I_L$  is non-negative, we choose  $V_{REF} = V_{SS}$ .

The ADC operates on a different supply; its ground will be different due to I-R drops and glitches. The differential input is tied to  $V_{REF}$ , so that its CMRR can reject differences between grounds.



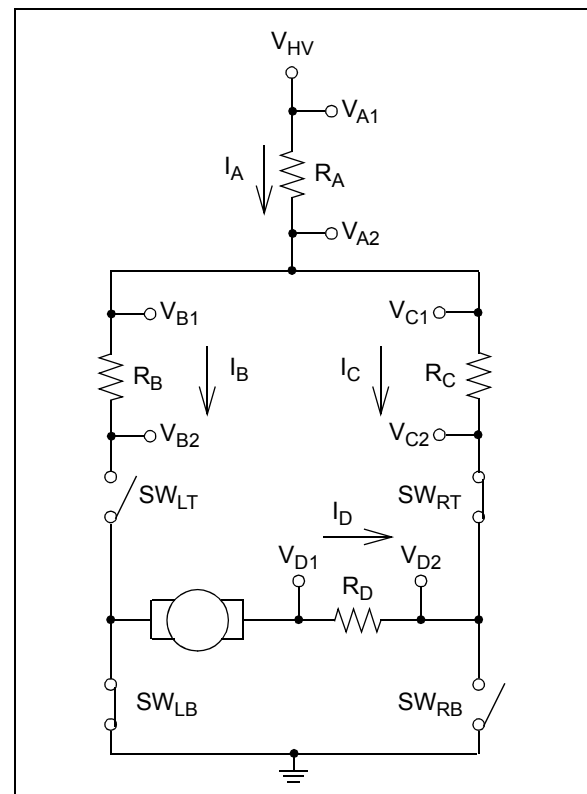
**FIGURE 5-9:** Motor Current Monitor for Regulated Supply Voltage.

H-Bridge motor drive circuits can place their current monitors in several positions. Figure 5-10 shows a few possibilities:

- Position A – This uses a unidirectional monitor (MCP6C02 at  $V_{A1}$  and  $V_{A2}$ ), with current polarity determined by the timing of the switches ( $SW_{LT}$ , etc.)
- Positions B and C – This uses two unidirectional monitors (on MCP6C02 at  $V_{B1}$  and  $V_{B2}$  and the other at  $V_{C1}$  and  $V_{C2}$ ), with each one representing one current polarity
- Position D – This uses a bidirectional monitor (MCP6C02 at  $V_{D1}$  and  $V_{D2}$ ), with current polarity determined by the output
  - The monitor must function at and below ground
  - The monitor must withstand large switching steps and glitches
  - We caution that the MCP6C02 should not be used in these conditions.

Obviously, choosing different locations for the monitor(s) gives trade-offs in accuracy and complexity. For instance, the monitor at Position D directly measures the motor current, but will have large voltage swings at its  $V_{IP}$  pin.

The switches are discrete semiconductor switches (i.e., CMOS, Bipolar, IGFET, etc.).



**FIGURE 5-10:** H-Bridge Motor Current Monitor, With a Few Possible Monitor Locations.

# MCP6C02

## 5.2.2 ANALOG LEVEL SHIFTER

The MCP6C02 can be used to shift analog voltages from a high positive voltage down to a low voltage. Many possibilities exist; Figure 5-11 is just one possible implementation.

The input attenuator ( $R_1$  and  $R_2$ ) allow a wider range of voltages to be measured. No resistor is placed between  $V_1$  and the noninverting input, so that the input current  $I_{BP}$  doesn't cause an offset shift. The attenuator resistors' accuracy and values may affect the circuit's gain error and offset.

The +2.5V reference level allows bidirectional voltage sensing; it needs to be very low impedance and reject glitches on the supply or ground (see Figure 5-3 for recommendations on this part of the circuit).

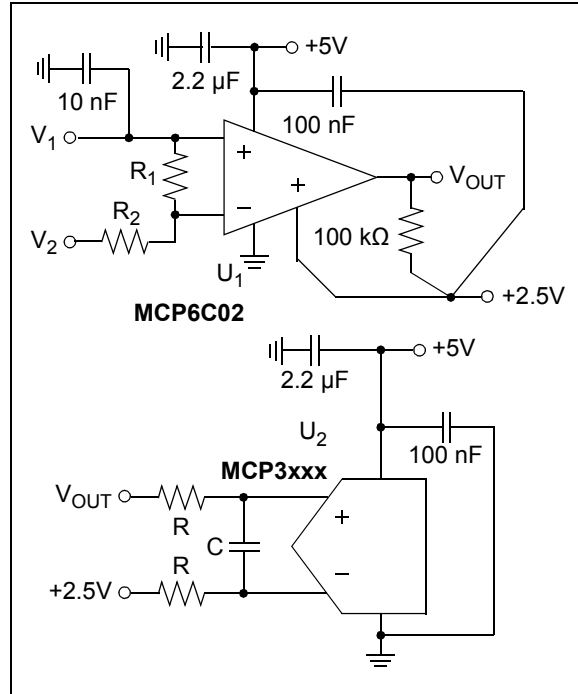
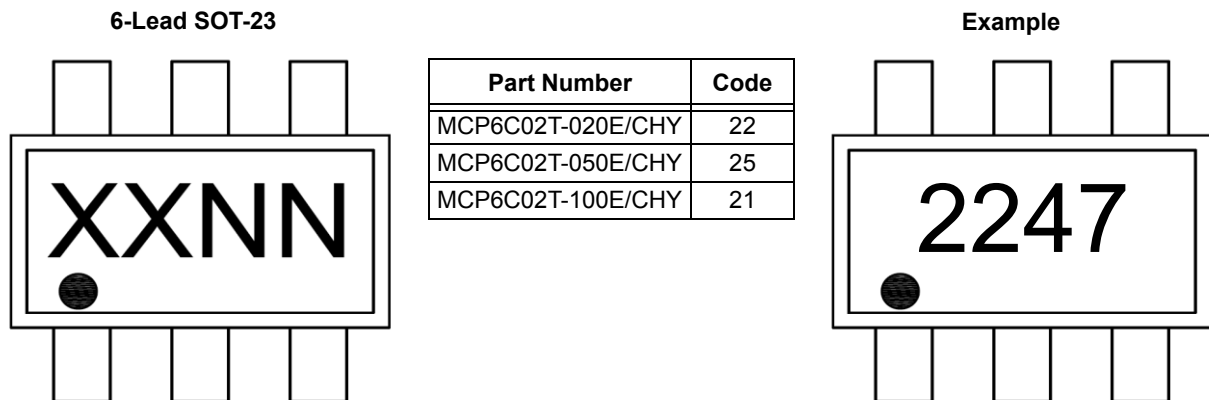


FIGURE 5-11: Analog Level Shifter.

## 6.0 PACKAGING INFORMATION

### 6.1 Package Marking Information

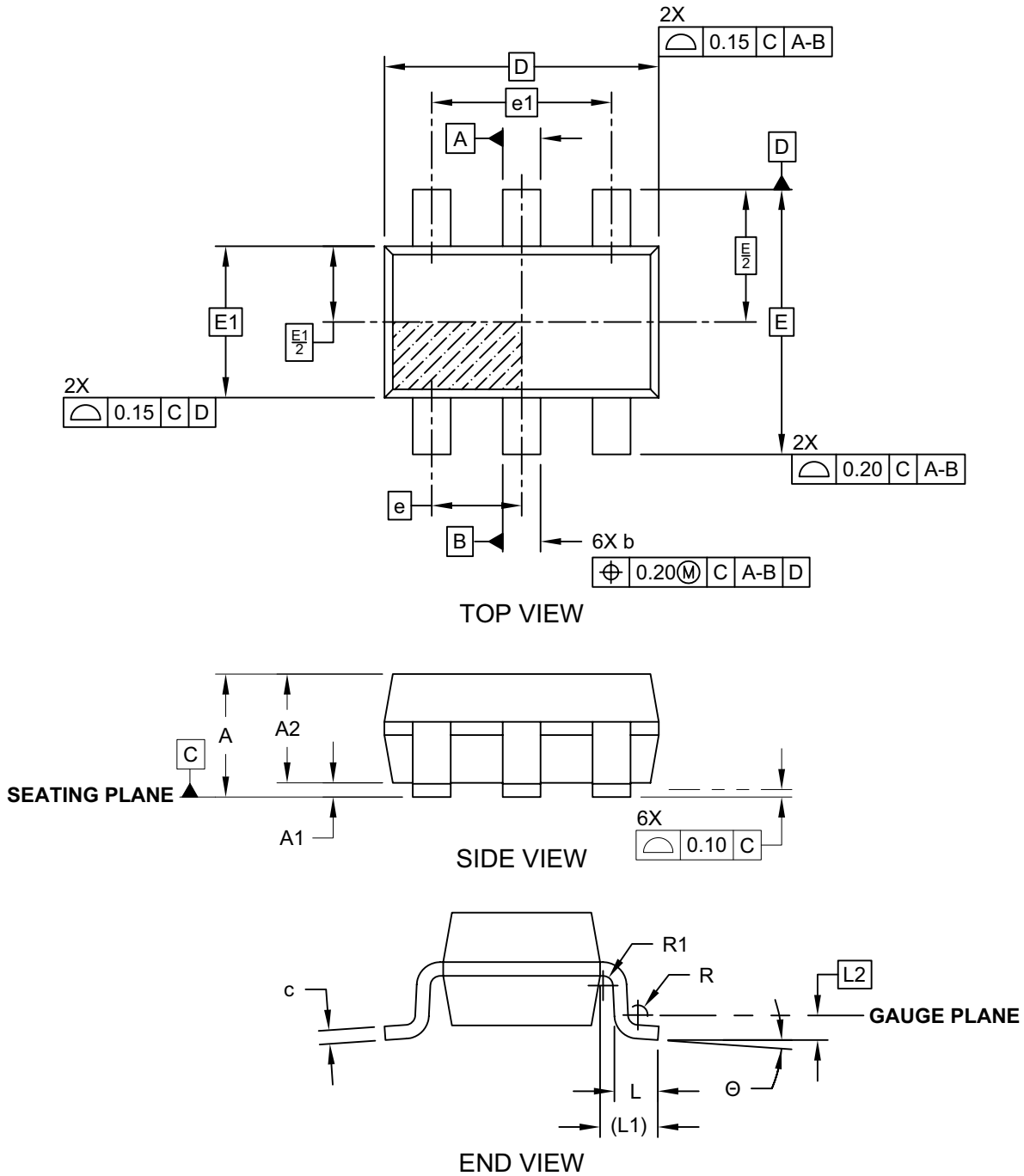


<b>Legend:</b>	XX...X	Device-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.
<b>Note:</b>	In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.	

# MCP6C02

## 6-Lead Plastic Small Outline Transistor (CH, CHY) [SOT-23]

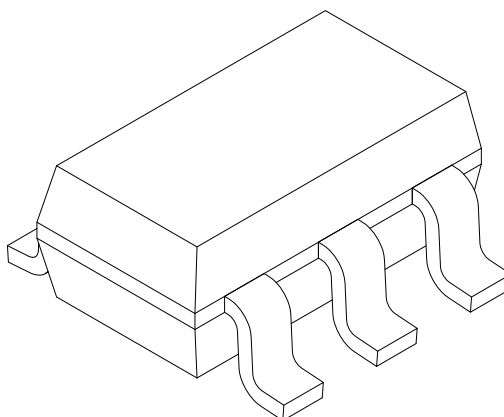
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Microchip Technology Drawing C04-028C (CH) Sheet 1 of 2

## 6-Lead Plastic Small Outline Transistor (CH, CHY) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Leads	N	6		
Pitch	e	0.95 BSC		
Outside lead pitch	e1	1.90 BSC		
Overall Height	A	0.90	-	1.45
Molded Package Thickness	A2	0.89	1.15	1.30
Standoff	A1	0.00	-	0.15
Overall Width	E	2.80 BSC		
Molded Package Width	E1	1.60 BSC		
Overall Length	D	2.90 BSC		
Foot Length	L	0.30	0.45	0.60
Footprint	L1	0.60 REF		
Seating Plane to Gauge Plane	L1	0.25 BSC		
Foot Angle	$\phi$	0°	-	10°
Lead Thickness	c	0.08	-	0.26
Lead Width	b	0.20	-	0.51

**Notes:**

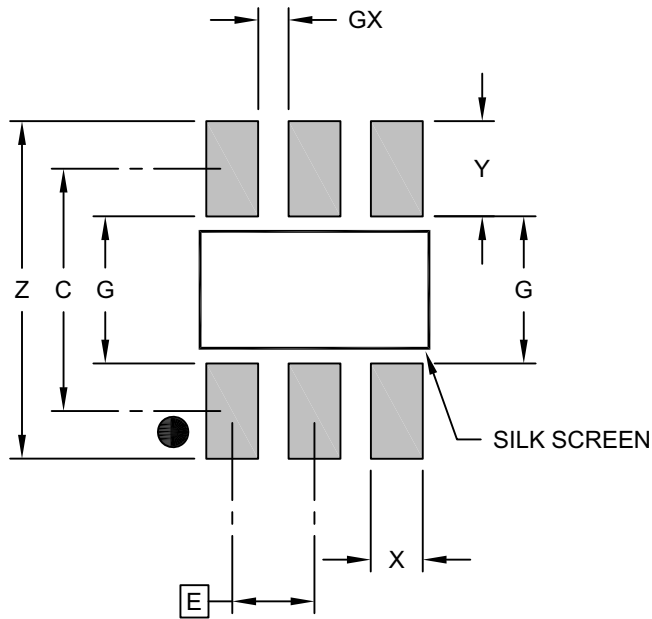
- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.25mm per side.
- Dimensioning and tolerancing per ASME Y14.5M  
 BSC: Basic Dimension. Theoretically exact value shown without tolerances.  
 REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-028C (CH) Sheet 2 of 2

# MCP6C02

## 6-Lead Plastic Small Outline Transistor (CH, CHY) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.95 BSC		
Contact Pad Spacing	C		2.80	
Contact Pad Width (X3)	X			0.60
Contact Pad Length (X3)	Y			1.10
Distance Between Pads	G	1.70		
Distance Between Pads	GX	0.35		
Overall Width	Z			3.90

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2028B (CH)

## APPENDIX A: REVISION HISTORY

### Revision A (November 2018)

- Initial release of this document.

NOTES:



## APPENDIX B: OFFSET TEST SCREENS

Input offset voltage specifications in the DC spec table (Table 1-1) are based on bench measurements (see Section 2.1, DC Precision). These measurements are much more accurate than at test, because:

- More compact circuit
- Parts soldered on the PCB
- More time spent averaging (reduced noise)
- Better temperature control
  - Reduced temperature gradients
  - Greater accuracy

We use production screens to support the quality of our  $V_{OS}$  specification in outgoing products. The screen limits are wider and are used to eliminate fliers; see Table B-1.

**TABLE B-1: OFFSET TEST SCREENS**

<b>Electrical Characteristics:</b> Unless otherwise indicated, $T_A = +25^\circ\text{C}$ , $V_{DD} = 2.0\text{V}$ to $5.5\text{V}$ , $V_{SS} = \text{GND}$ , $V_{IP} = 34\text{V}$ , $V_{DM} = 0\text{V}$ , $V_{REF} = V_{DD}/4$ , $V_L = V_{DD}/2$ and $R_L = 10\text{ k}\Omega$ to $V_L$ ; see Figure 1-9 and Figure 1-10.						
Parameters	Sym.	Min.	Max.	Units	Gain	Conditions
input Offset Voltage	$V_{OS}$	-34	+34	$\mu\text{V}$	20	Test Screen
		-24	+24		50	
		-20	+20		100	

NOTES:

## PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO.</u>	<u>[X]<sup>(1)</sup></u>	<u>-XXX</u>	<u>X</u>	<u>/XXX</u>	<b>Examples:</b>
Device	Tape and Reel Option	Gain Option	Temperature Range	Package	
<b>Device:</b> MCP6C02: Zero-Drift, 65V High-Side Current Sense Amp					a) MCP6C02T-020E/CHY: Tape and Reel, Differential Gain = 20, Extended Temperature, 6LD SOT-23
<b>Tape and Reel Option:</b> T = Tape and Reel <sup>(1)</sup>					b) MCP6C02T-050E/CHY: Tape and Reel, Differential Gain = 50, Extended Temperature, 6LD SOT-23
<b>Gain Option:</b> 020 = Differential Gain of 20 V/V 050 = Differential Gain of 50 V/V 100 = Differential Gain of 100 V/V					c) MCP6C02T-100E/CHY: Tape and Reel, Differential Gain = 100, Extended Temperature, 6LD SOT-23
<b>Temperature Range:</b> E = -40°C to +125°C (Extended)					<b>Note 1:</b> Tape and Reel identifier only appears in the catalog part number description. This identifier is used for ordering purposes and is not printed on the device package. Check with your Microchip Sales Office for package availability with the Tape and Reel option.
<b>Package:</b> CHY = Plastic Small Outline Transistor (SOT-23), 6-Lead					

# MCP6C02

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NOTES:

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**Note the following details of the code protection feature on Microchip devices:**

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
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- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as “unbreakable.”

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